

# Status of the activity on development of Data Concentrator Chip

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on behalf of ASIC lab at NRNU MEPhI*

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V. Samsonov, A. Serazetdinov, V. Shumikhin*

*VI-th Collaboration Meeting of the MPD Experiment  
October 28, 2020*

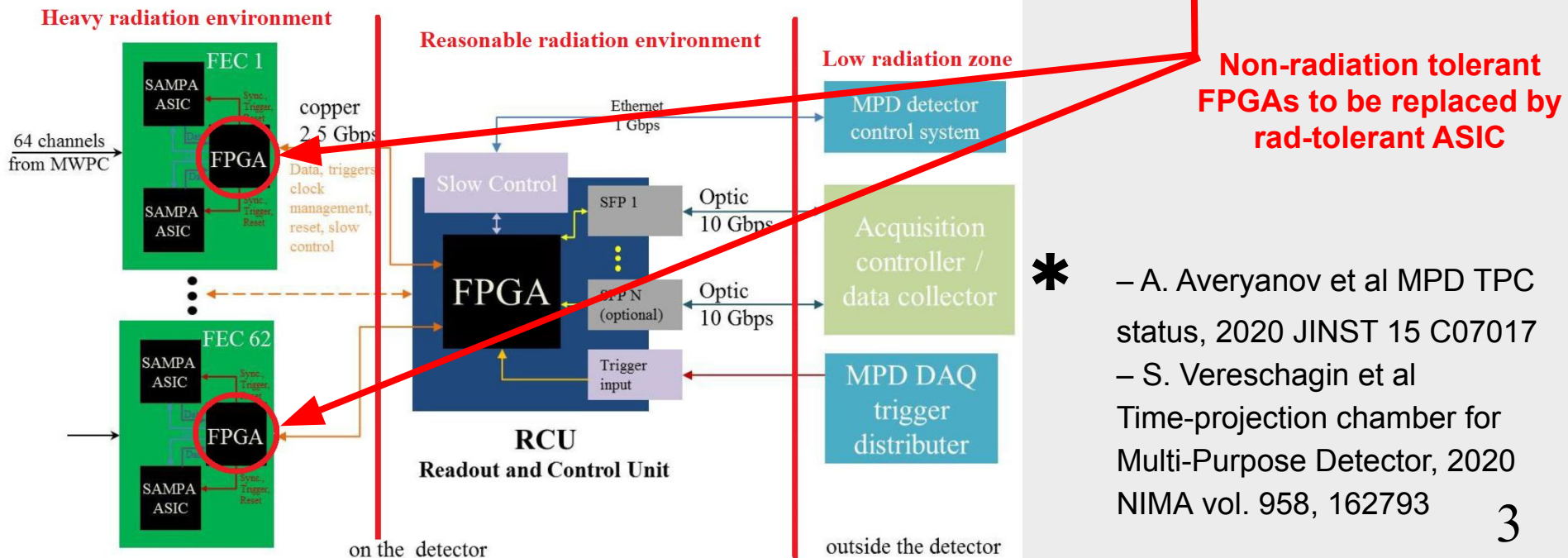
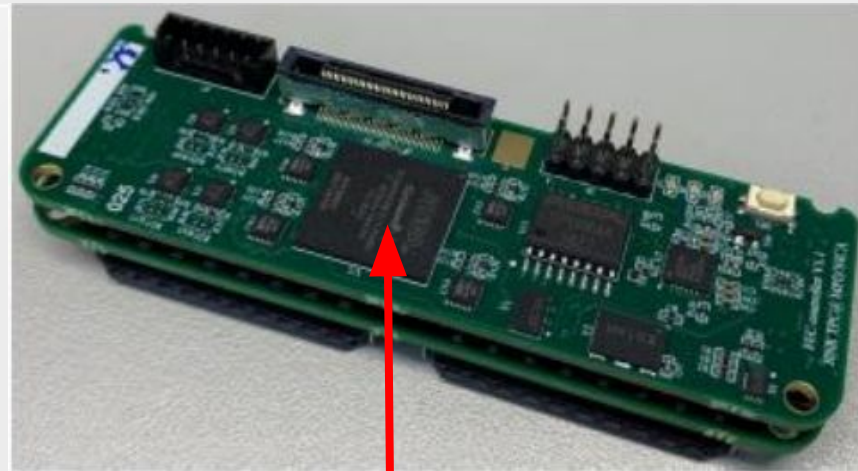
# Outline

- Starting point
- Chip designation & environment
- Design routes
- Specifications
- Features & building blocks
- ASIC block diagram
- External interfaces and protocols
- Process & Layout & Pinout & Bonding
- Radiation tolerance issue
- Further plans & conclusions

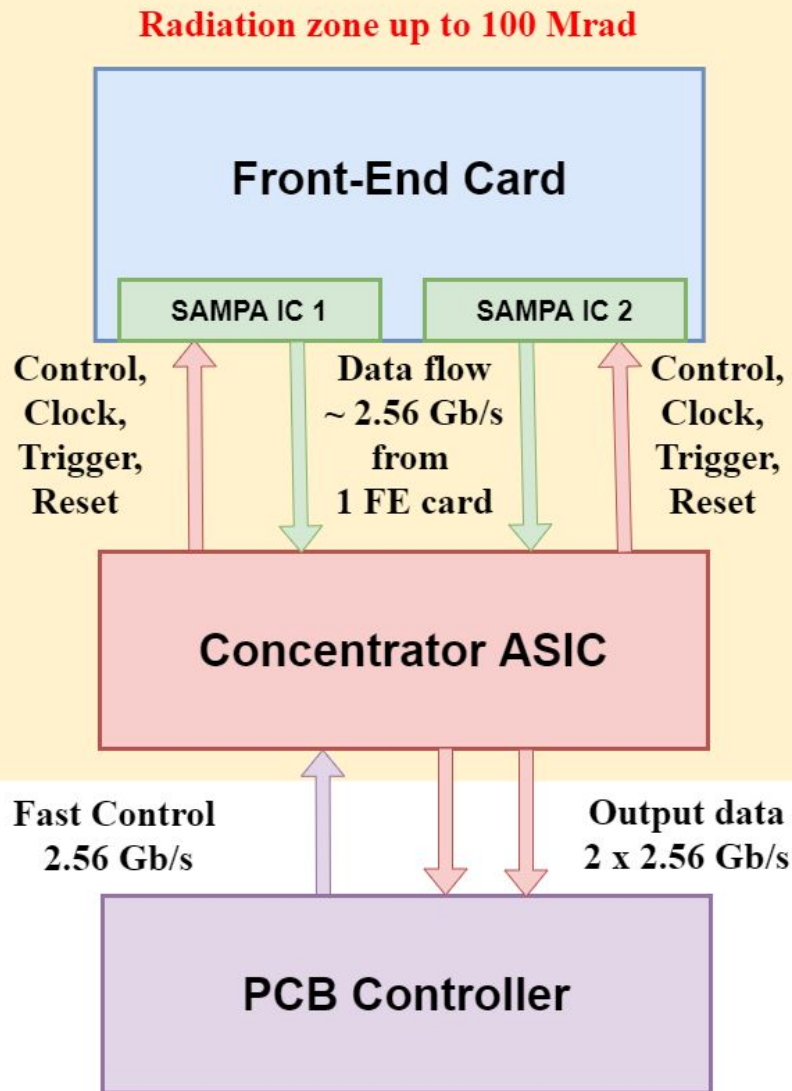
# TPC FEE\* as a starting point



2 PCBs  
28\*91 mm<sup>2</sup>



# The prototype chip features



- almost double redundancy for data flow: 2.56 Gb/s one totally at SAMPA outputs goes via two CML interfaces at the same speed each
- radiation tolerance fits the most heavy radiation zone
- compensation of the used cable losses as well as PCB and package parasitics
- programmable built-in chip 50 Ohm matching for cables

# Why does the concentrator ASIC necessary for TPC FEE?

- The TPC setup contains about  $10^5$  detector channels, based on SAMPAs chips, ended by high-speed ( $\sim 10$  Mb/s) high-resolution (10 bit) ADCs, generates a large **amount of** digital **data** and thus require a high integration, based on ASIC technology
- Data should proceed via a synchronized deserialization, sequencing, noise-free and fault-free encoding, output serialization
- Needs to use a very limited number but **high-speed links** both for data transfer out and control. All possible RF losses should be mitigated
- Needs to process the data on-detector in a non-friendly **radiation environment**
- Non-availability of COT components ready to use

# Hub ASIC shortly

- **Transceiver** chip (called as “hub v.1”) for FEE communication to/from counting room
- 1 downlink + 2 uplinks, both working at **2.56 Gb/s** via electrical cables
- **Radiation tolerant** by design (up to 100 MRad)
- Functionality: detector data readout, triggers, clocks, control and calibration



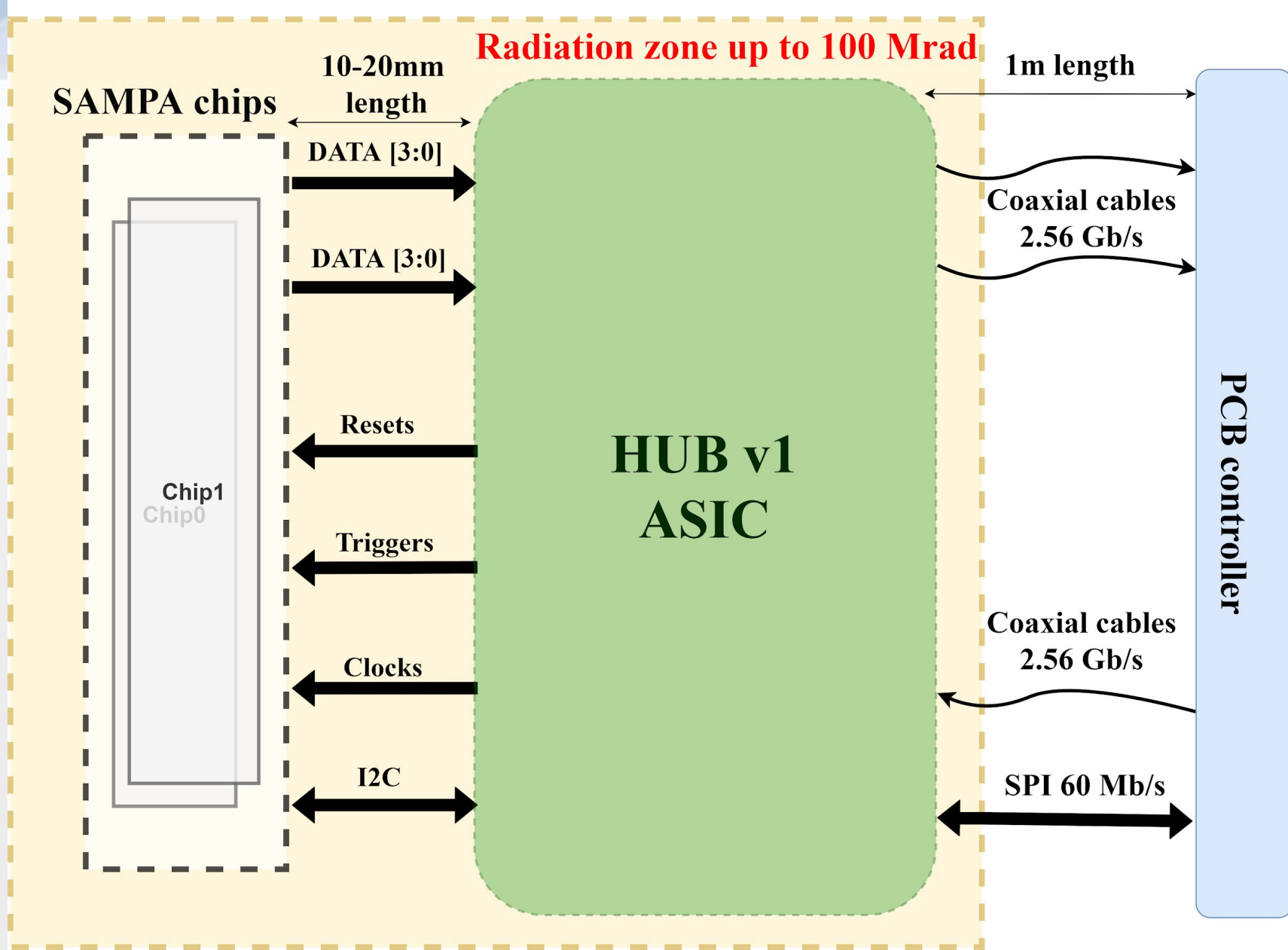
# ASIC designation

- HUB v1 is a radiation tolerant prototype ASIC that can be used to implement multi purpose high speed bidirectional links for TPC FEE
- ASIC supports one or two 1m length 2.56 Gb/s links in the direction from detectors to the counting room (Uplink) and one 1m 2.56 Gb/s link in the direction from counting room to the detectors (Downlink)

## *Interfaces:*

- 2x4 ports SAMPA data
- 2x ports SAMPA Reset
- 2x3 ports SAMPA Trigger
- 2x3 ports SAMPA Clock
- 2x CML Tx
- CML Rx
- SPI (slow control)
- I2C

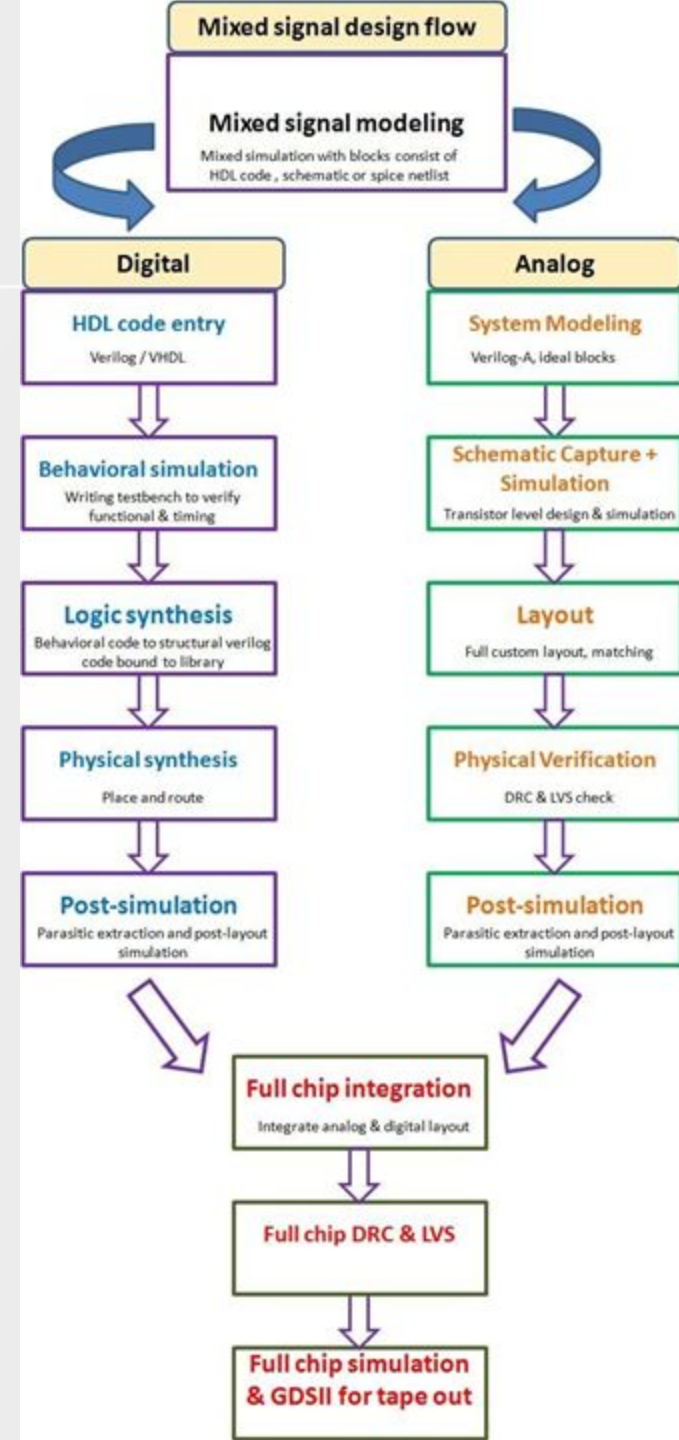
# Environment





# Standard mixed-mode design route

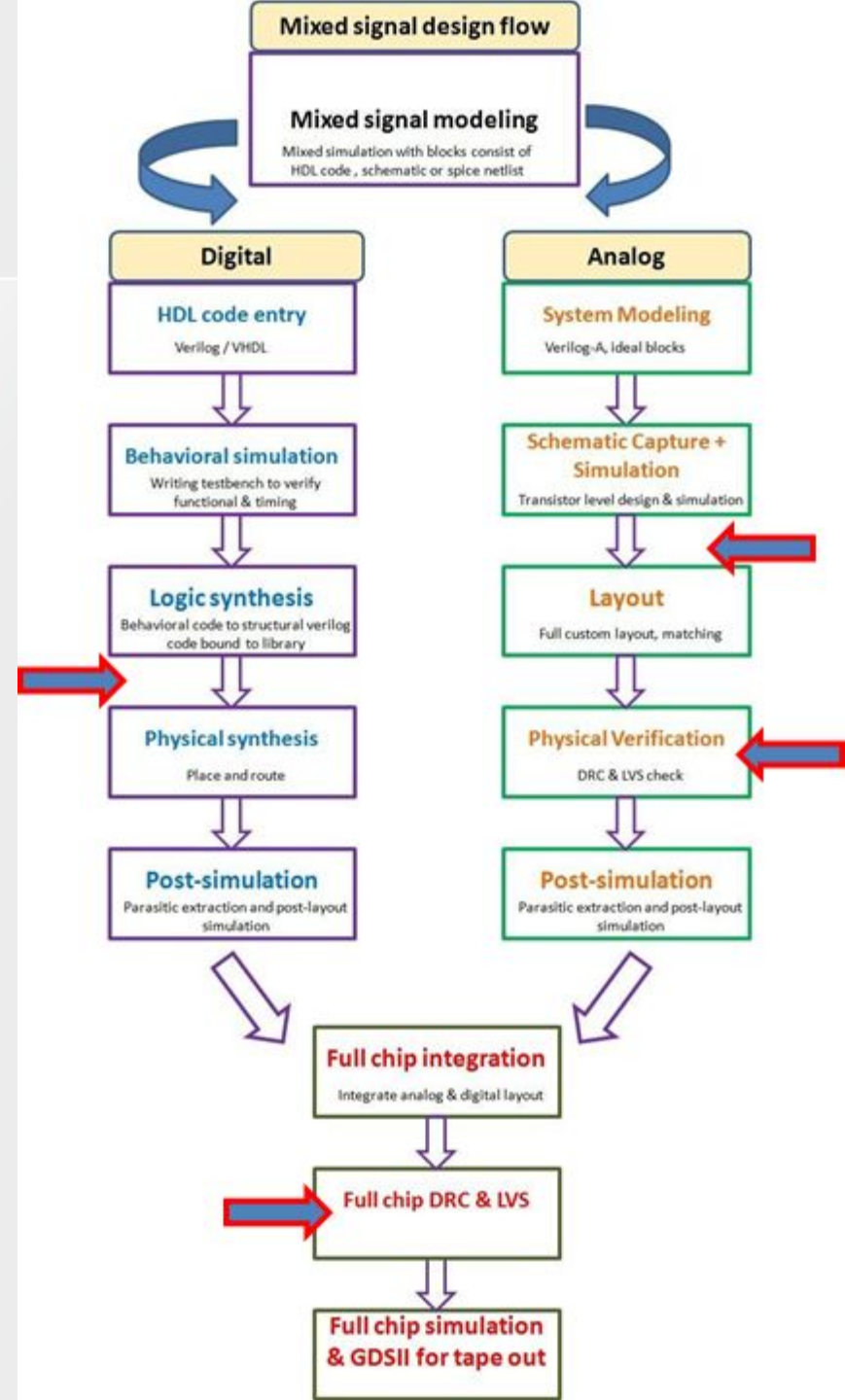
- Cadence CAD tools for start-to-finish design flow
- Top-to-bottom design
- TSMC DKs for the 65 nm process
- Powerful servers (DELL, INTEL) + client workstations
- Digital on top and mostly digital flow



# Radiation tolerance aspects in design

Legend →

- Digital part uses: 12T standard cell library of TSMC 65 nm process and triplication logic
- Analog part uses different known tips and tricks to provide radiation hardness by:
  - process
  - design
  - schematics implementation



# Specifications (1)

Specifications	Value
Technology node	65 nm
I/O voltage	2,5 V
CORE voltage	1,2 V
Temperature	0 - 85 °C
Power consumption	< 1 W
Radiation tolerance	< 100 Mrad
Serial interface with SAMPA	
Number of input channels	8 channel (16 pins)
Maximum input frequency	320 MHz
Physical level	SLVS

# Specifications (2)

## High speed Interface to counting room

Number of channels	Input	1
	Outputs	2
Frequency	2.56 GHz	
Physical level	CML	
Transmission distance	< 1 meter	

## I2C Interface

Operating mode	10 bit addressing
Frequency	100 kHz - 5 MHz
Physical level	LVCMOS 1.2 V

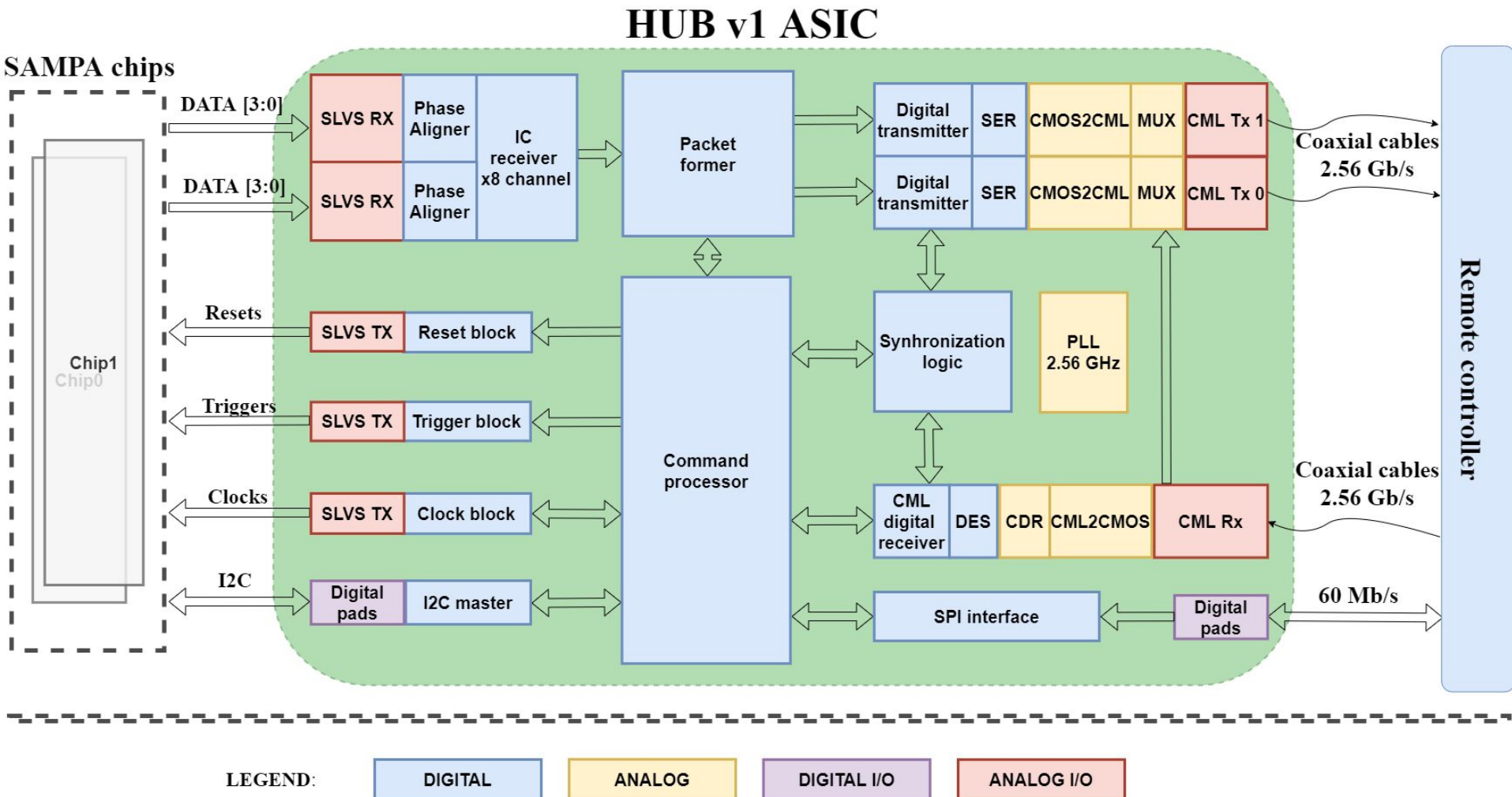
## Synchronization Interface

Number of channels	6 channel
Frequencies	20/40/80/160/320 MHz
Physical level	SLVS

# Specifications (3)

Output trigger links	
Number of links	6
Physical level	SLVS
Output reset links	
Number of links	2
Physical level	SLVS
Hardware address	
Number of links	4
Physical level	LVCMOS 1.2 V
External LDO control	
Number of links	2
Physical level	LVCMOS 1.2 V

# Prototype ASIC block diagram



Mixed-mode (mostly digital (~70%)) design

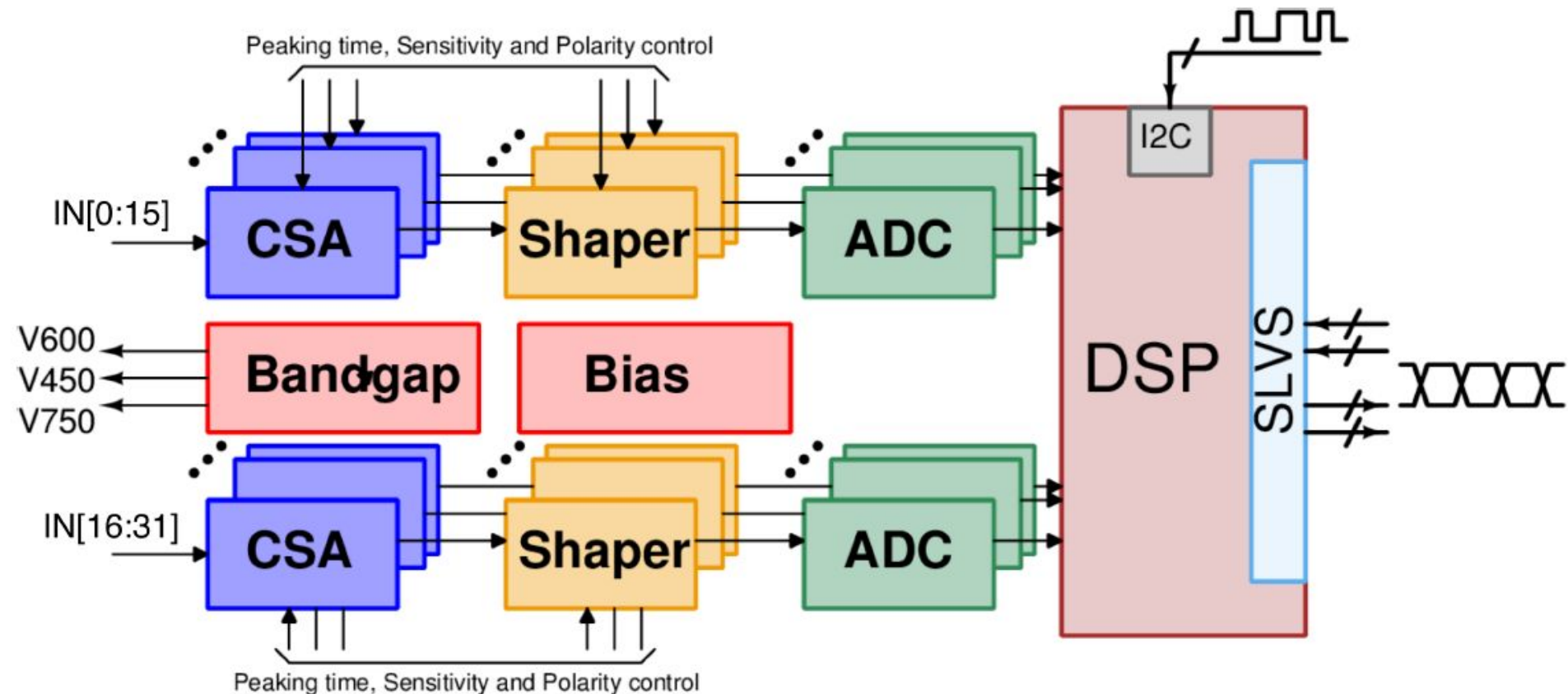


# Building blocks

<i><b>Analog blocks</b></i>	<i><b>Digital blocks</b></i>	
SLVS Rx	IC receiver channel	I2C master
SLVS Tx	Phase Aligner	DES
CML_RX	Packet former	Reset
CML_TX	Digital Transmitter	Trigger
PLL	SER	Clock
CDR	Synhronization Logic	
POR	SPI Interface	
CMOS2CML	Command processor	

# Getting data from SAMPA\*

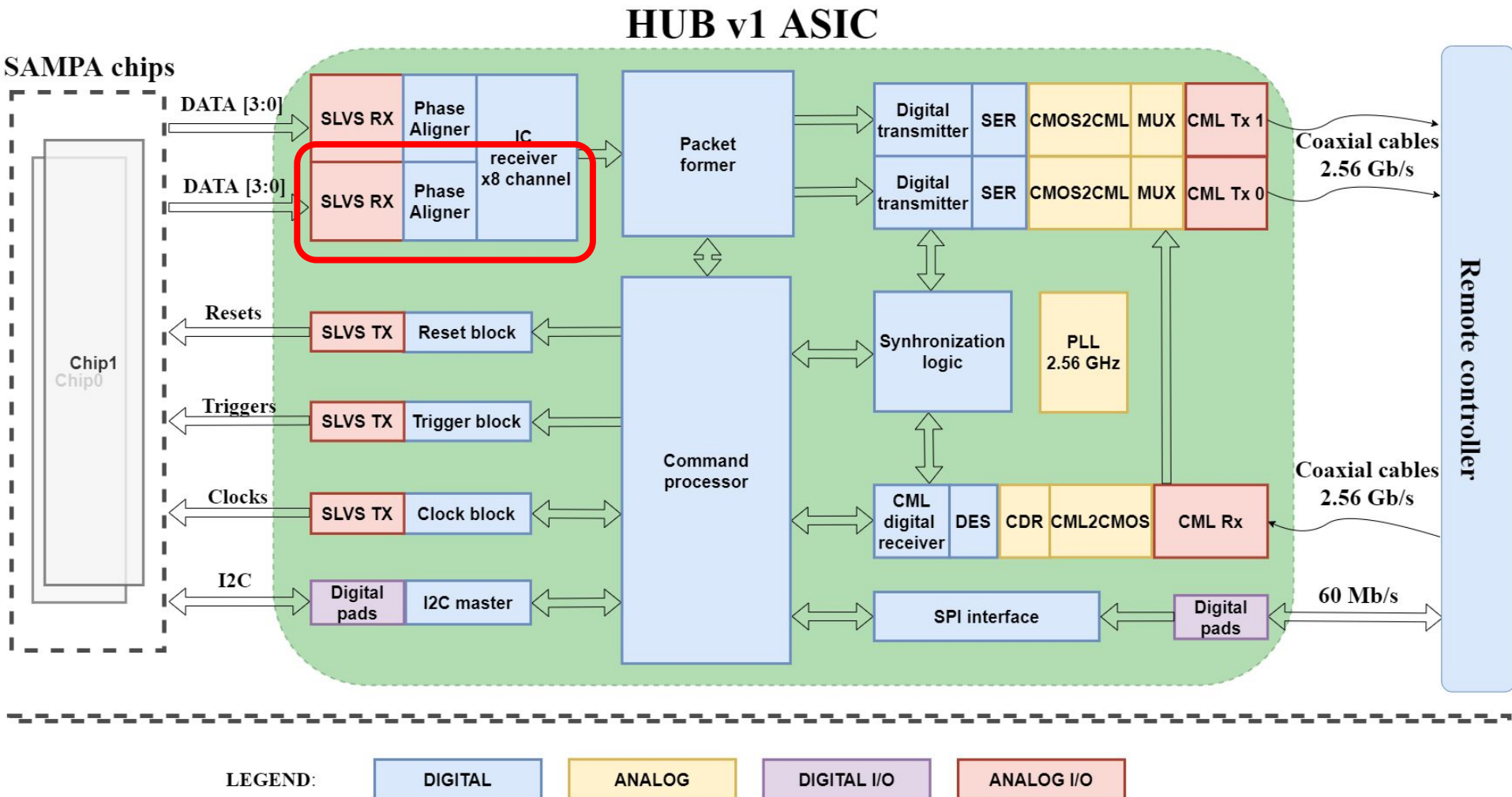
(SAMPA itself)



- \* – J. Adolfsson, et al. SAMPA chip: the new 32 channels ASIC for the ALICE TPC and MCH upgrades, 2017 JINST 12 (04) C04008

# Getting data from SAMPA

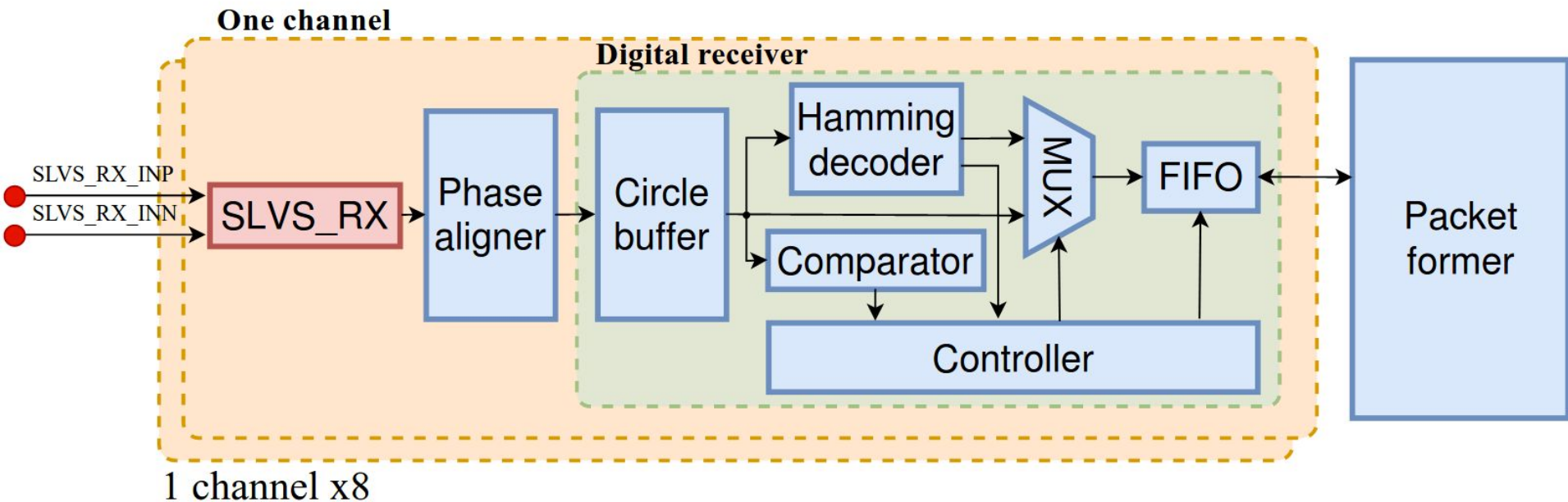
## (HUB Digital receiver block)



Mixed-mode (mostly digital (~70%)) design

# Getting data from SAMPA

## (Digital receiver structure)



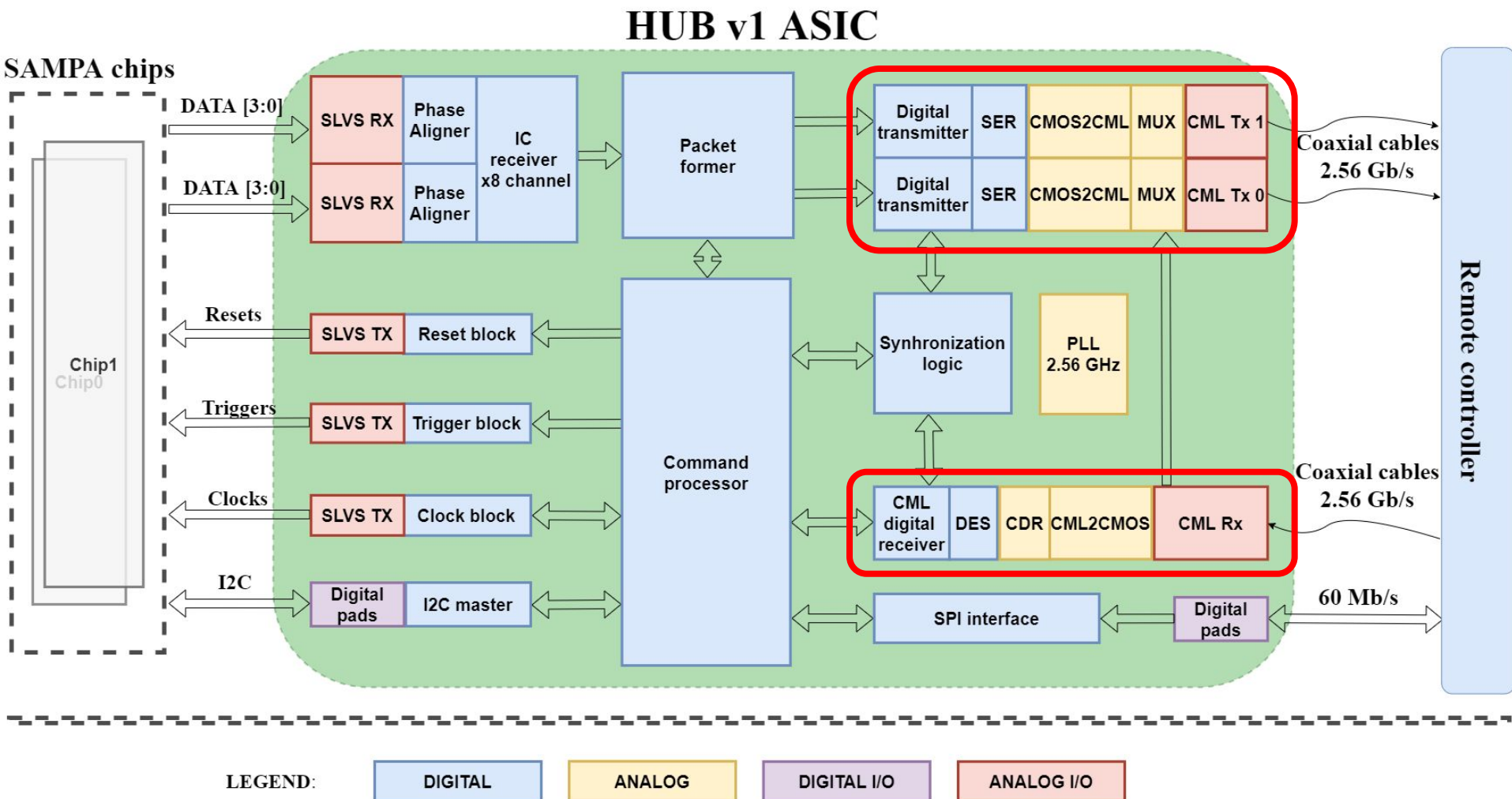
**LEGEND:**

**ANALOG I/O**

**DIGITAL**

● - Analog pad

# High speed interface to counting room



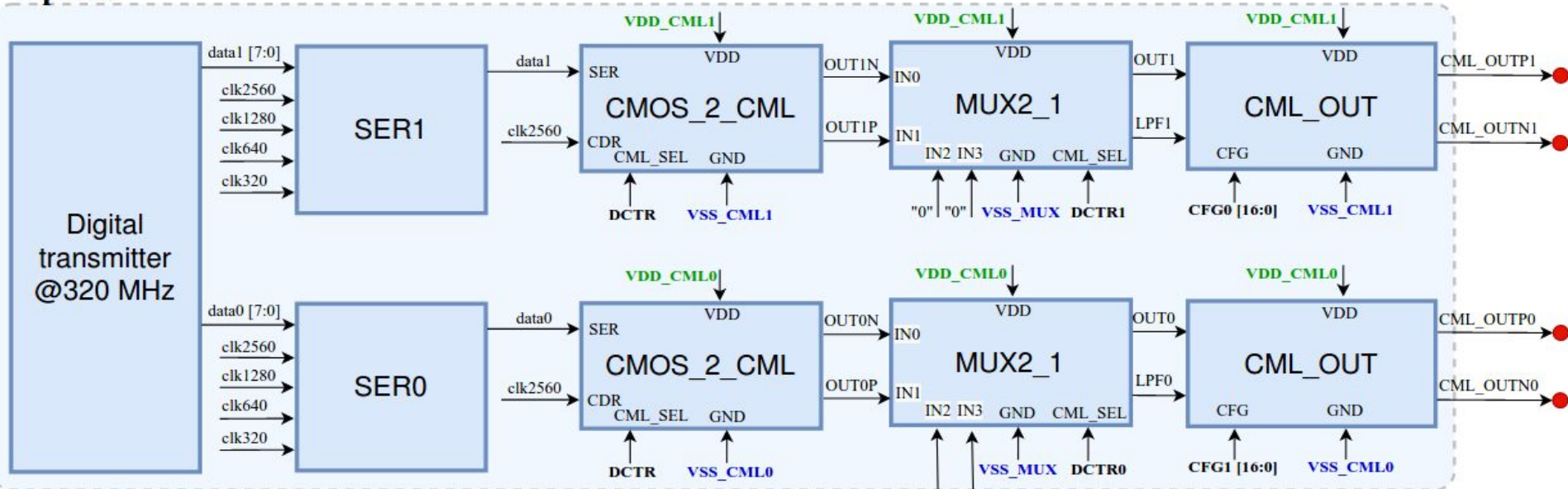
Mixed-mode (mostly digital (~70%)) design



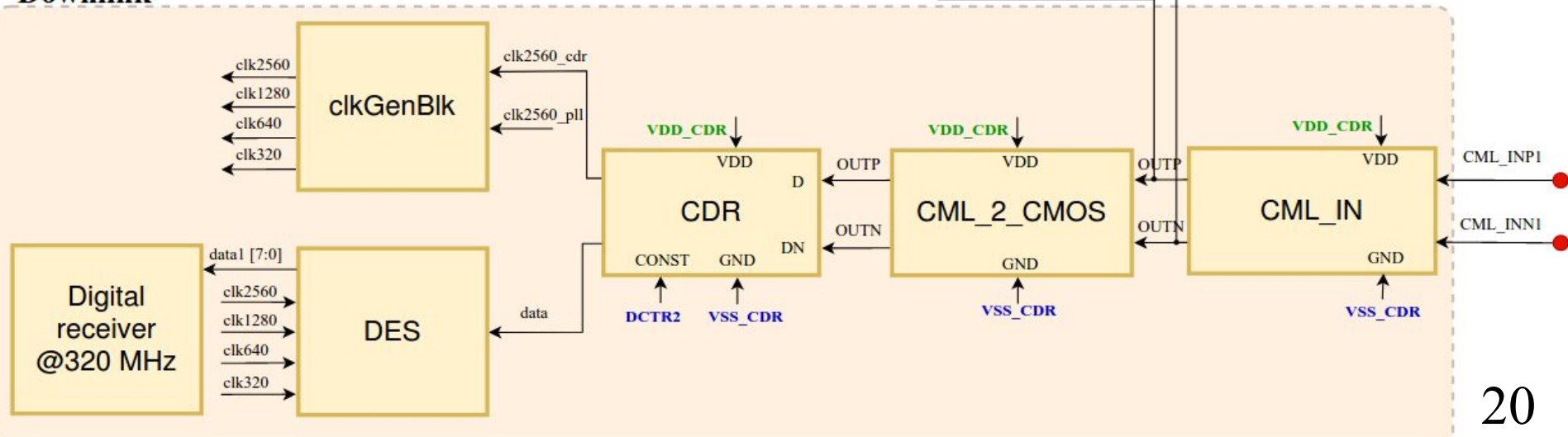
# High speed interface to counting room

## (Tx & Rx details)

### Uplink



### Downlink





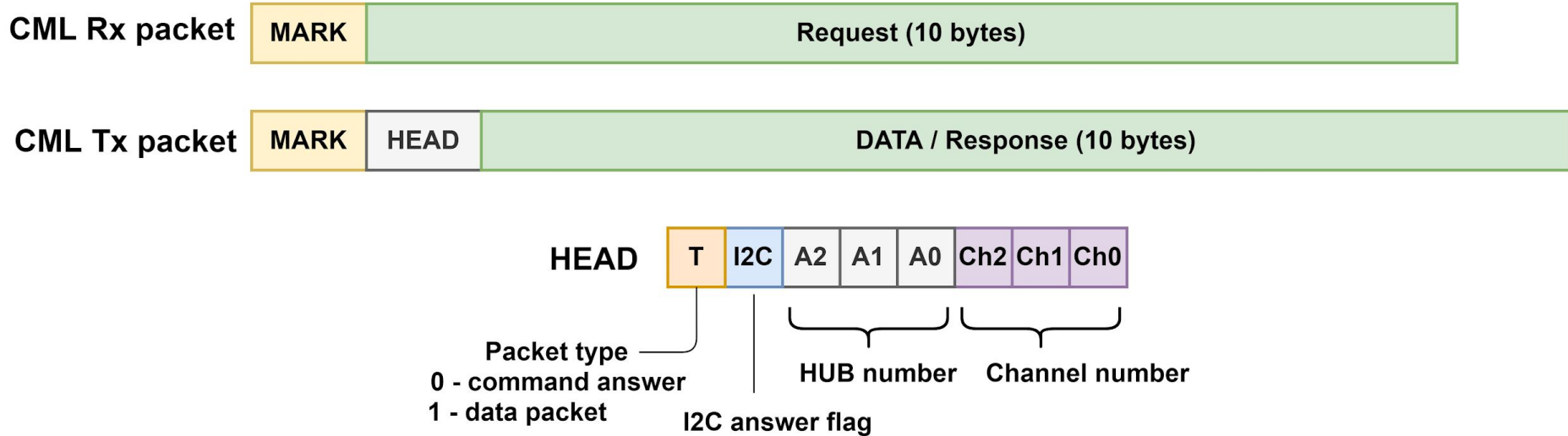
# High speed interface to counting room

(main CML interface features)

- CML data are encoded by 8b/10b
- CML Rx receives command request
- Supported modes are: one or two CML
- CML Tx 0 translates command response and SAMPA data  
(commands have higher priority than data)
- CML Tx 1 translates SAMPA data if CML Tx 0 is busy and two CML Tx are used

# CML protocol

## (Rx & Tx packets)

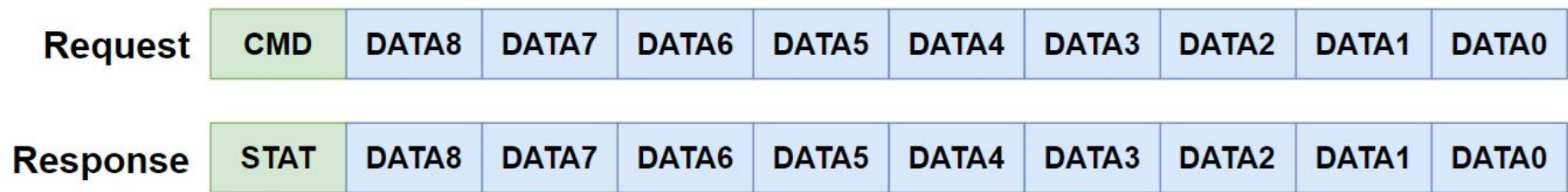


At T=0 packet contains command Response

At T=1 packet contains 10 bytes DATA

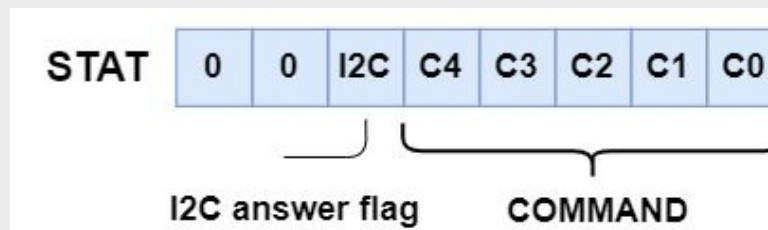
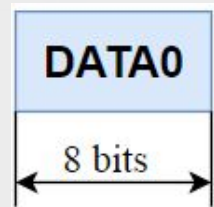
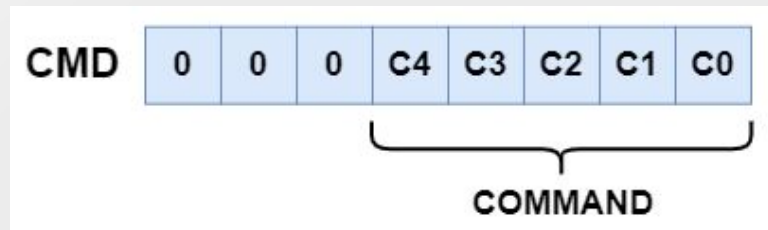
# CML protocol

(format of commands)



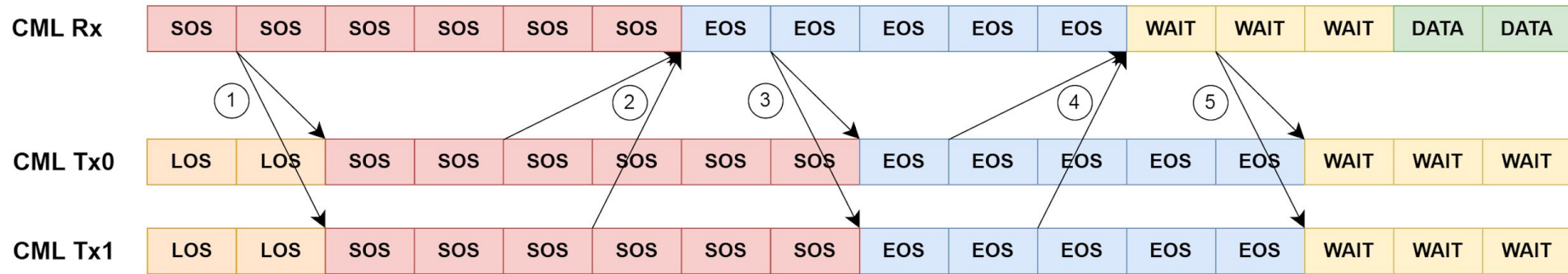
## ***Commands:***

- Config load
- Config read
- ASIC Soft Reset
- SAMPA Trigger out
- SAMPA reset
- I2C read
- I2C write
- Debug commands



# CML protocol

## (synchronization procedure)



### Steps:

- 1) ASIC starts of synchronization
- 2) Controller synchronize both channels
- 3) ASIC sends EOS
- 4) Controller finalize synchronization
- 5) ASIC finalize synchronization

### CML modes:

- LOS (lost of sync) - K28.4
- SOS (start of sync) - K28.1
- EOS (end of sync) - K28.3
- WAIT - K28.5
- Data packet
- Command packet

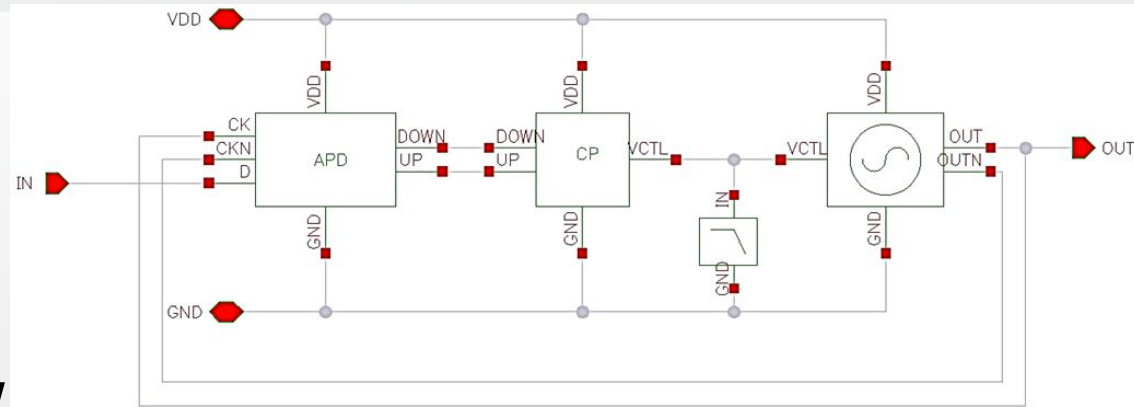
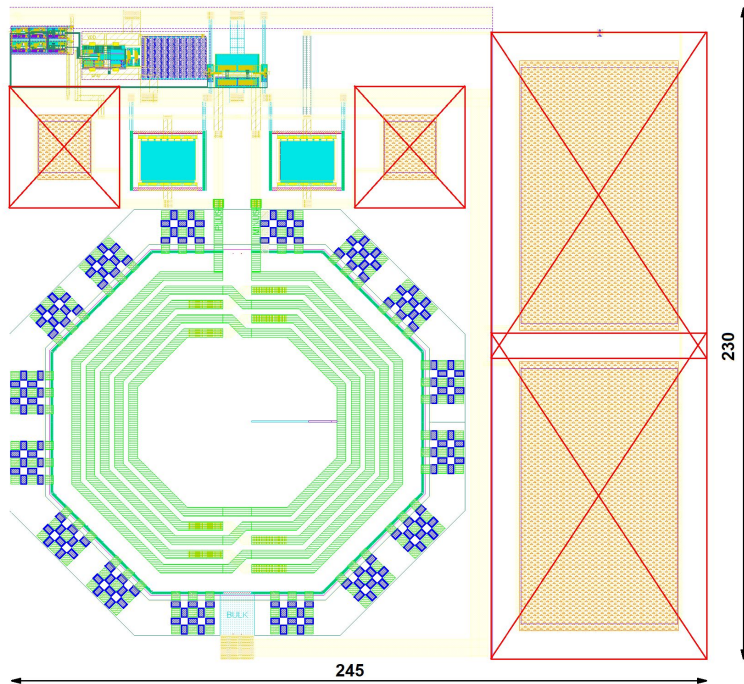
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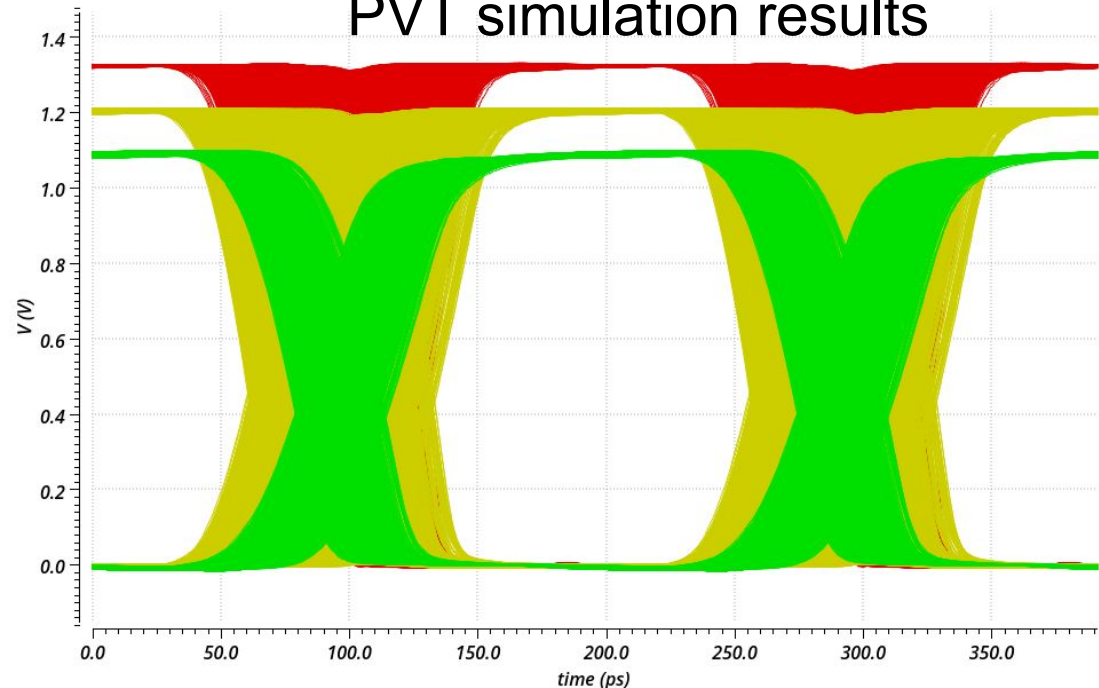
# Clock Data Recovery

## Alexander phase detector scheme

- frequency setting  $< 1 \mu\text{s}$
- jitter about 70 ps
- duty cycle 48.5 %
- power consumption: 6 mW



## PVT simulation results





# Process & Layout block placement

**Chip size: 2 x 2 mm**

# TSMC 65nm CMOS

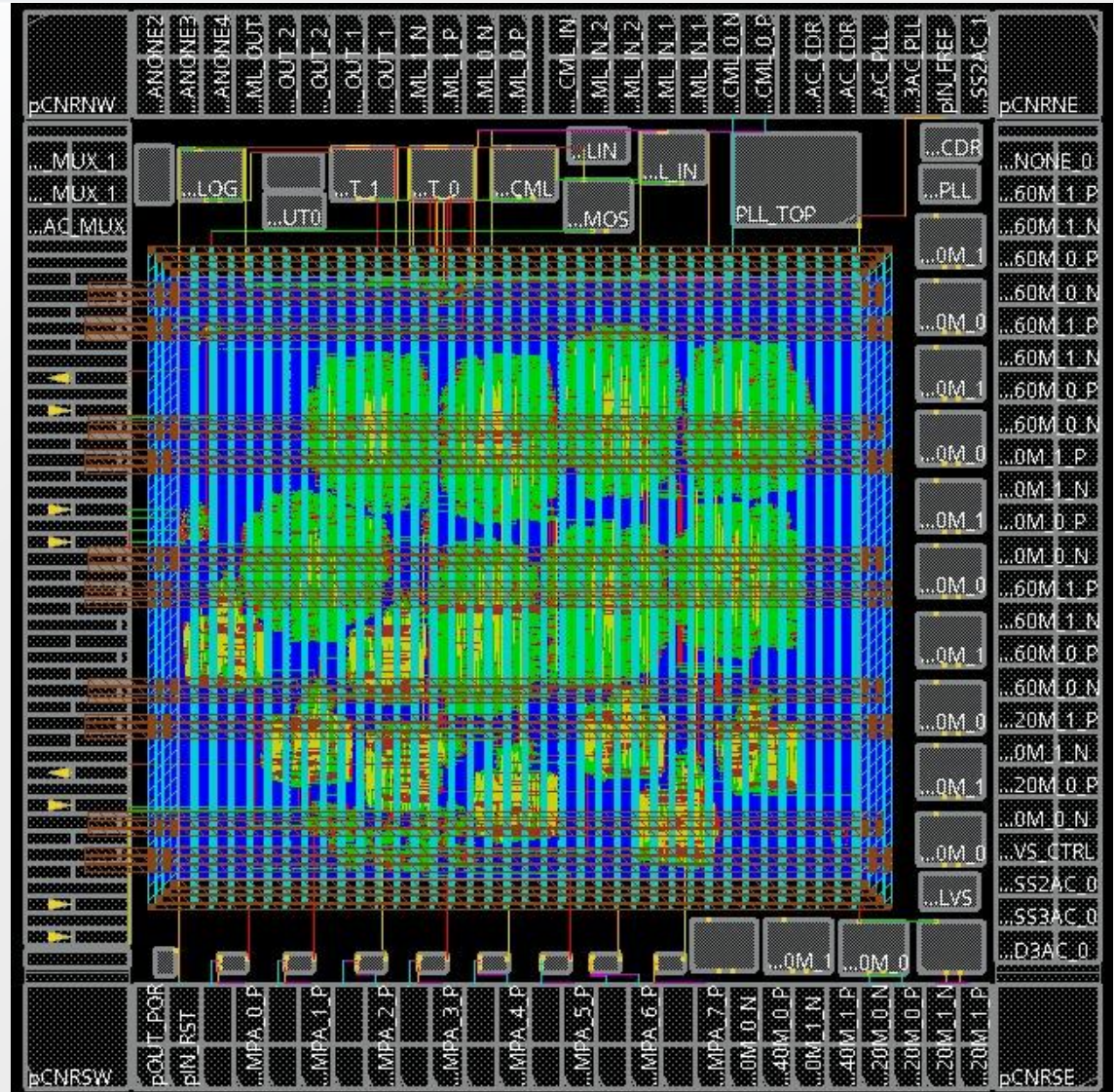
## Mixed-Signal/RF, Low Power

Core : 1.2 V, IO : 2.5 V

## Metal scheme:

1P9M\_6X1Z1U

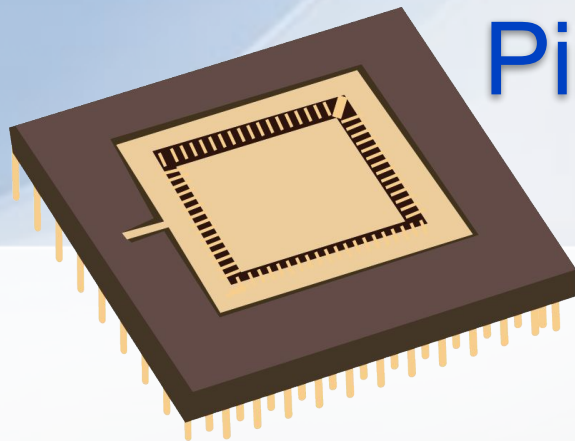
12T standard cells for  
digital part



# 115 IO pads

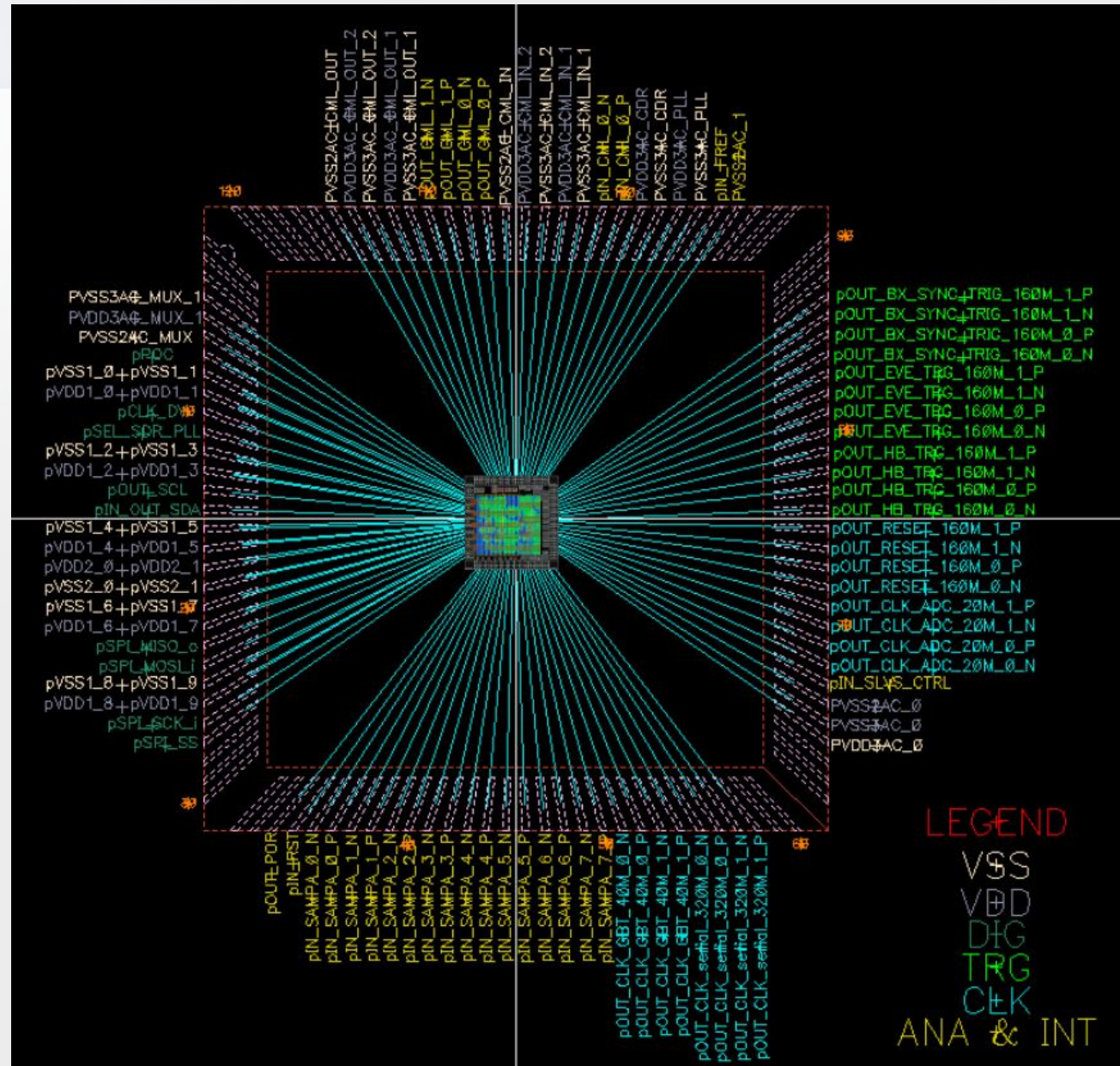


# Pinout & Bonding & Packaging



**CPGA 120**

Such a packaging  
produces parasitics,  
resulting in needs to  
perform accurate RF  
simulations



# Transmission line attenuation

## AlphaWire 9436

### coax cable

*Specifications (1 m)*

Wave impedance –  **$50 \pm 5 \Omega$**

Insulator – **PFA**

Dissipation factor – **0.0008 @**

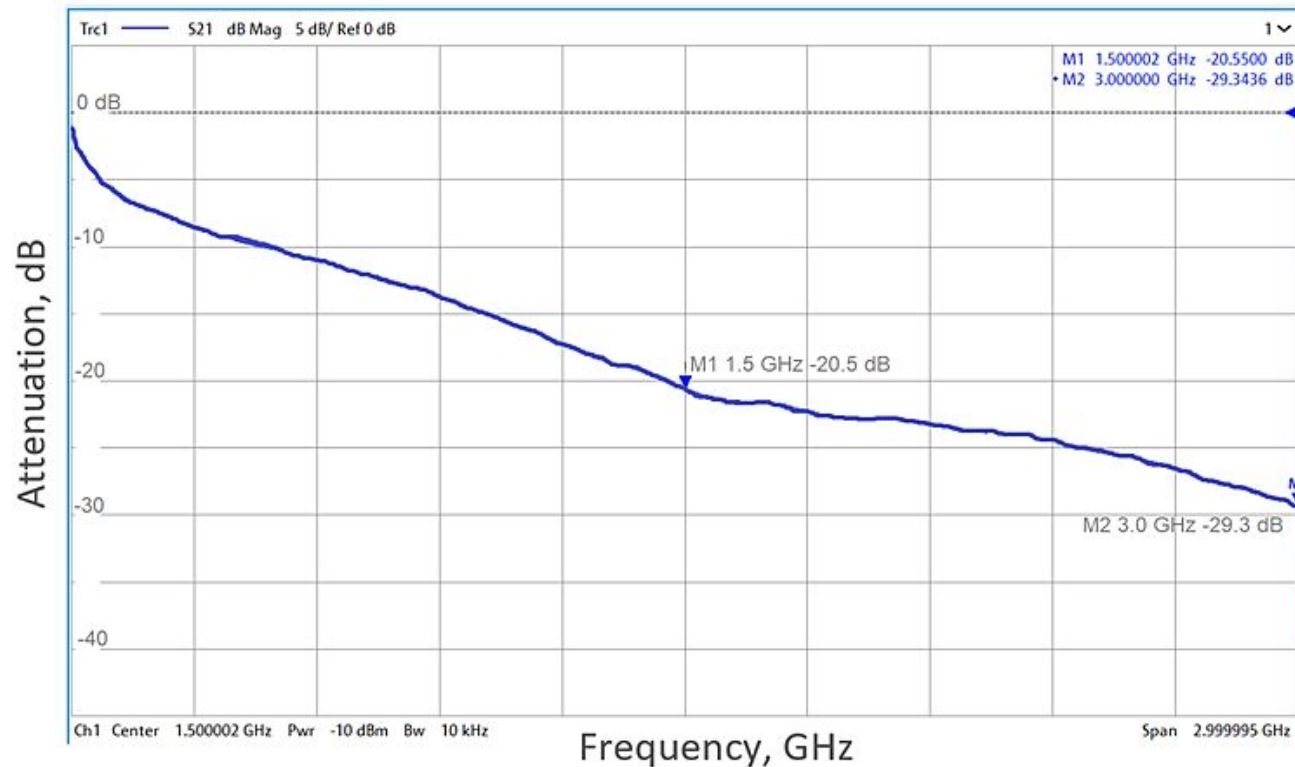
**1 GHz**

Dielectric constant – **2.11**

DCR –  **$1.57 \Omega/\text{m}$**

Attenuation, dB/m – **-0.25 @**

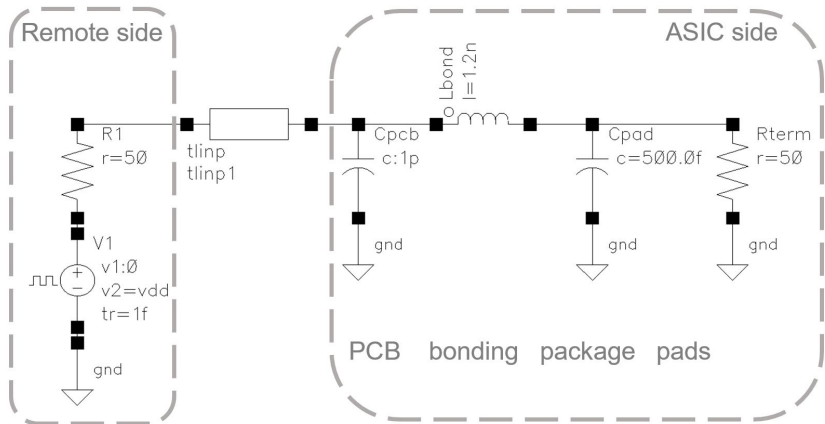
**10 MHz**



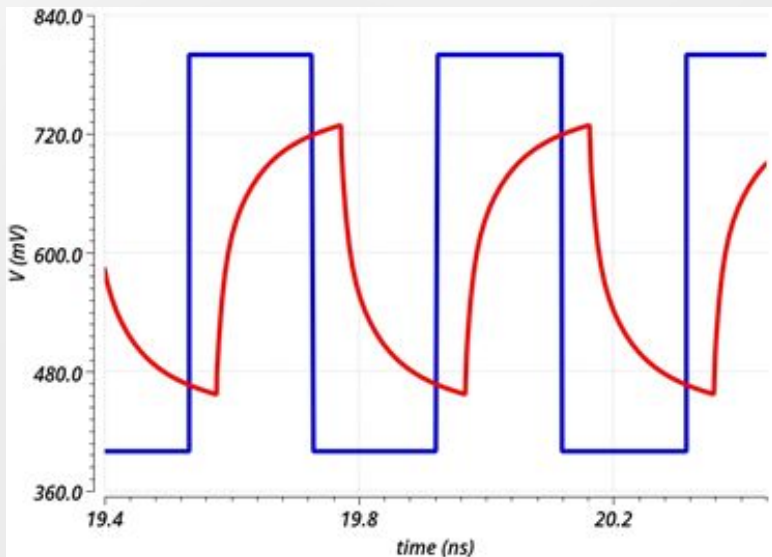
Attenuation of 5 m AWG36 cable,  
measured by TPC team (JINR) on 20.10.2020

# Transmission line model

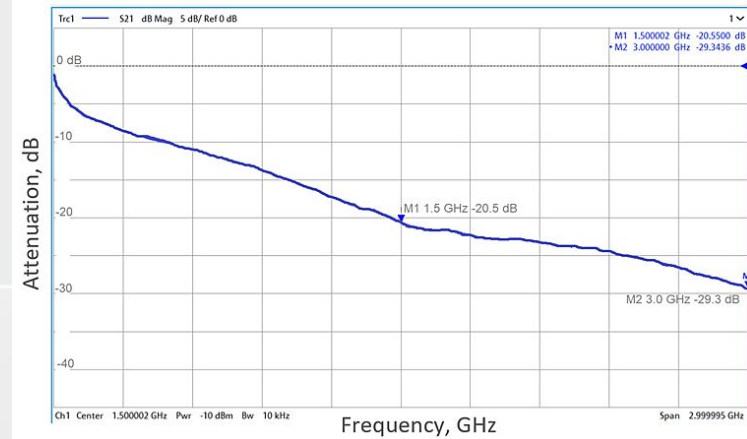
## (measurement versus simulation)



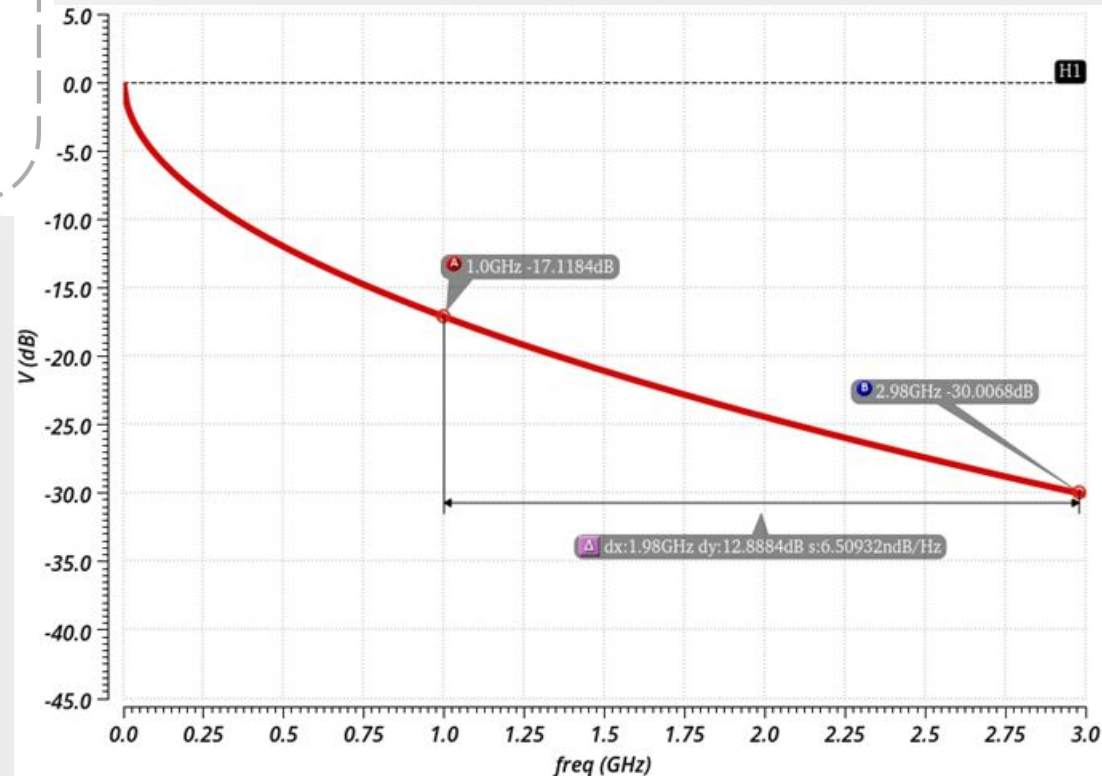
CML interface parasitics (LPF)



1 m cable losses at 2.56 Gb/s



5m cable attenuation vs frequency (measurement)



5m cable attenuation vs frequency (simulation)

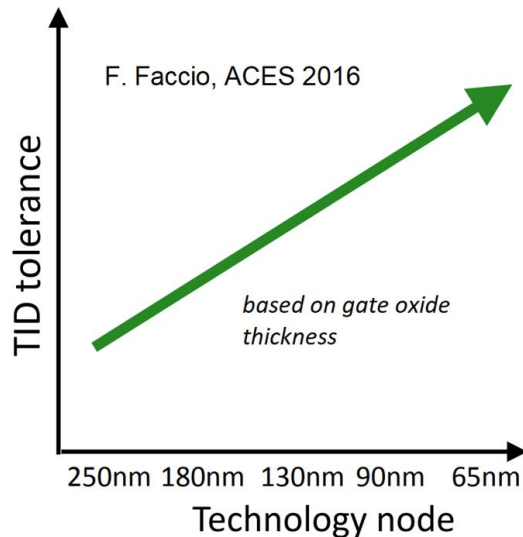


# Radiation tolerance by ...

*(used tips and tricks)\**

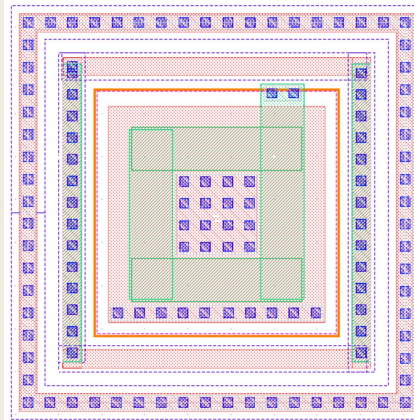
## Process

- **valuable trade-offs** on performance and radiation tolerance at a reasonable cost
- thin gate oxide provides **improved TID tolerance**



## Design

- **ELT NMOS transistors** have been used to reduce leakage due to TID
- **double guard rings** around p-wells and n-wells, biased to constant voltages, have been used to prevent single event latch-ups



## Schematics

- high-impedance nodes have been **low pass filtered** to suppress single event upsets
- **short channel** (<120 nm) transistors have been avoided to prevent RISCE effect
- **triple modular redundancy** have been used for the most critical digital blocks
- **12T instead of 7T or 9T** standard cells were employed

\*see References

## Technology

TSMC 65nm CMOS Logic or Mixed-Signal/RF,  
Low Power\*

Jan

Feb

Mar

Apr

## May

Jun

Jul

Aug

Sep

Oct

Nov

Dec

19

13

19

18

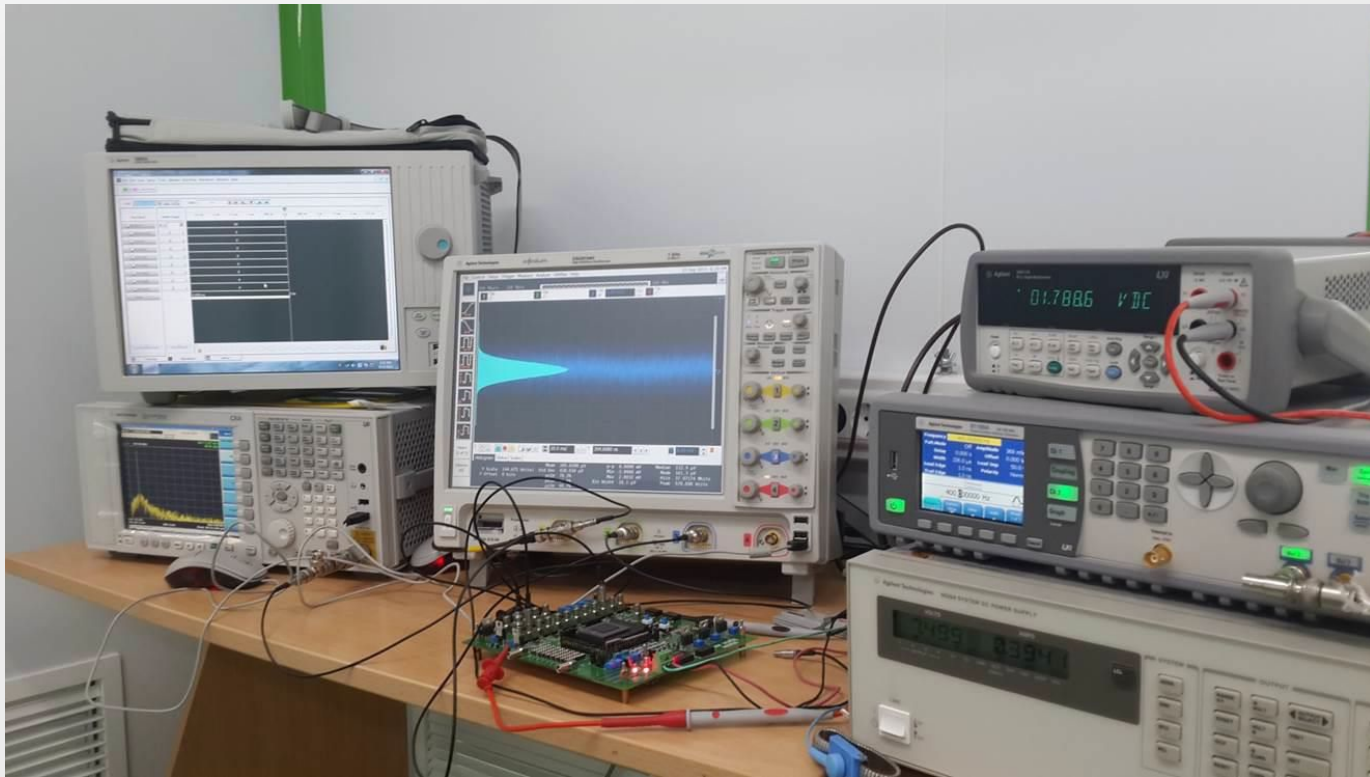
**Nov. 18, 2020** – deadline for ASIC GDSII submission for prototyping via Europractice miniasic program

Sponsorship for fabrication is a responsibility of MPD team from JINR



# Further plans (2021)

- Design of breadboard (PCB) & measurement technique
- Lab functional tests of prototyped ASICs
- Study of ASIC radiation tolerance at PNPI, Gatchina



# Conclusions

- Method for front-end (on-detector) data concentration has been developed
- It has been implemented in the prototype radiation tolerant CMOS ASIC, intended for the TPC FEE
- Prototype ASIC will be submitted for fabrication via Europractice soon (on Nov. 18)
- Lab functional tests of ASICs as well as their radiation tolerance tests are expected as next steps

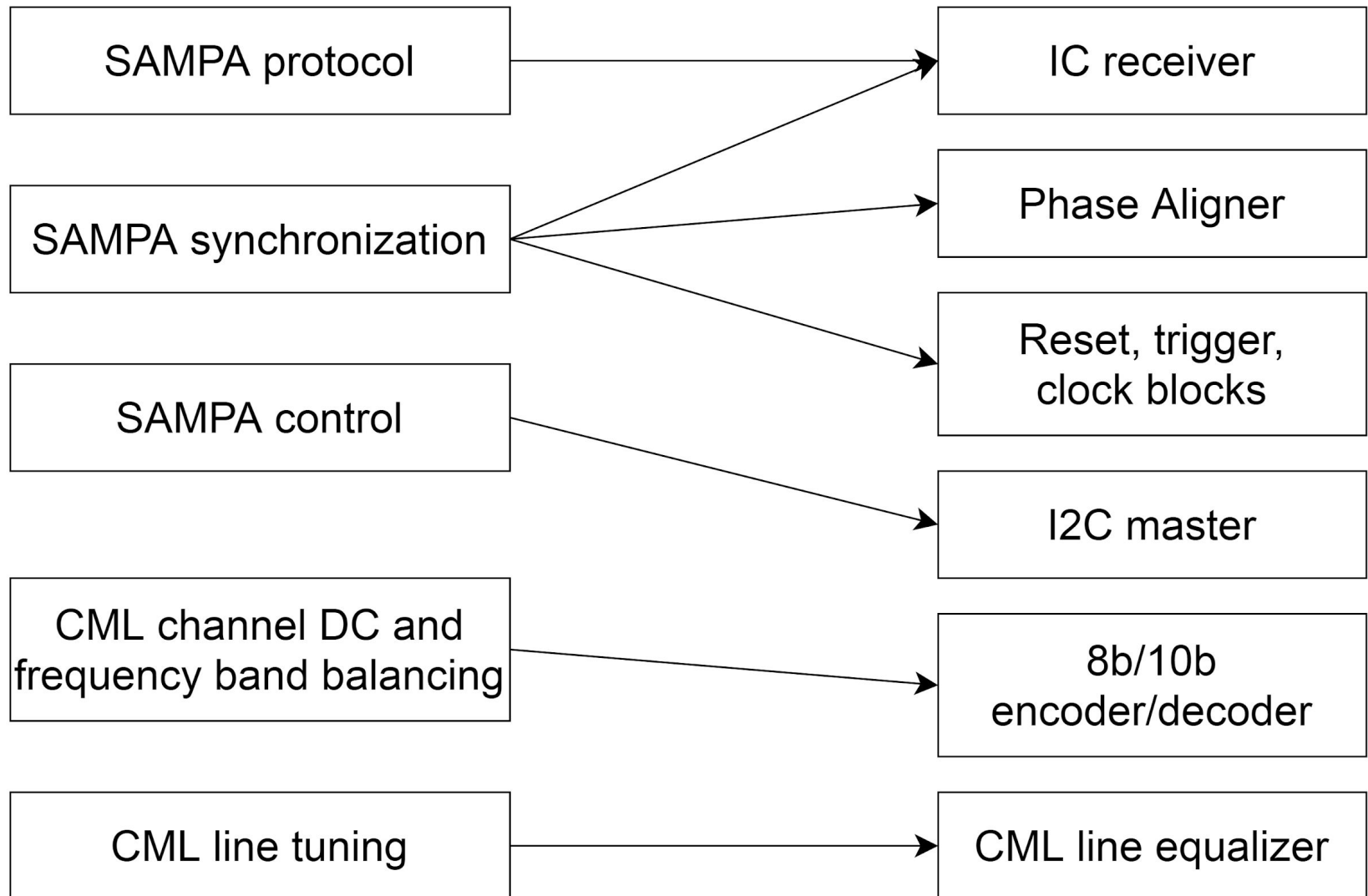
Thank you  
for attention

**Back up slides**

# Features

&

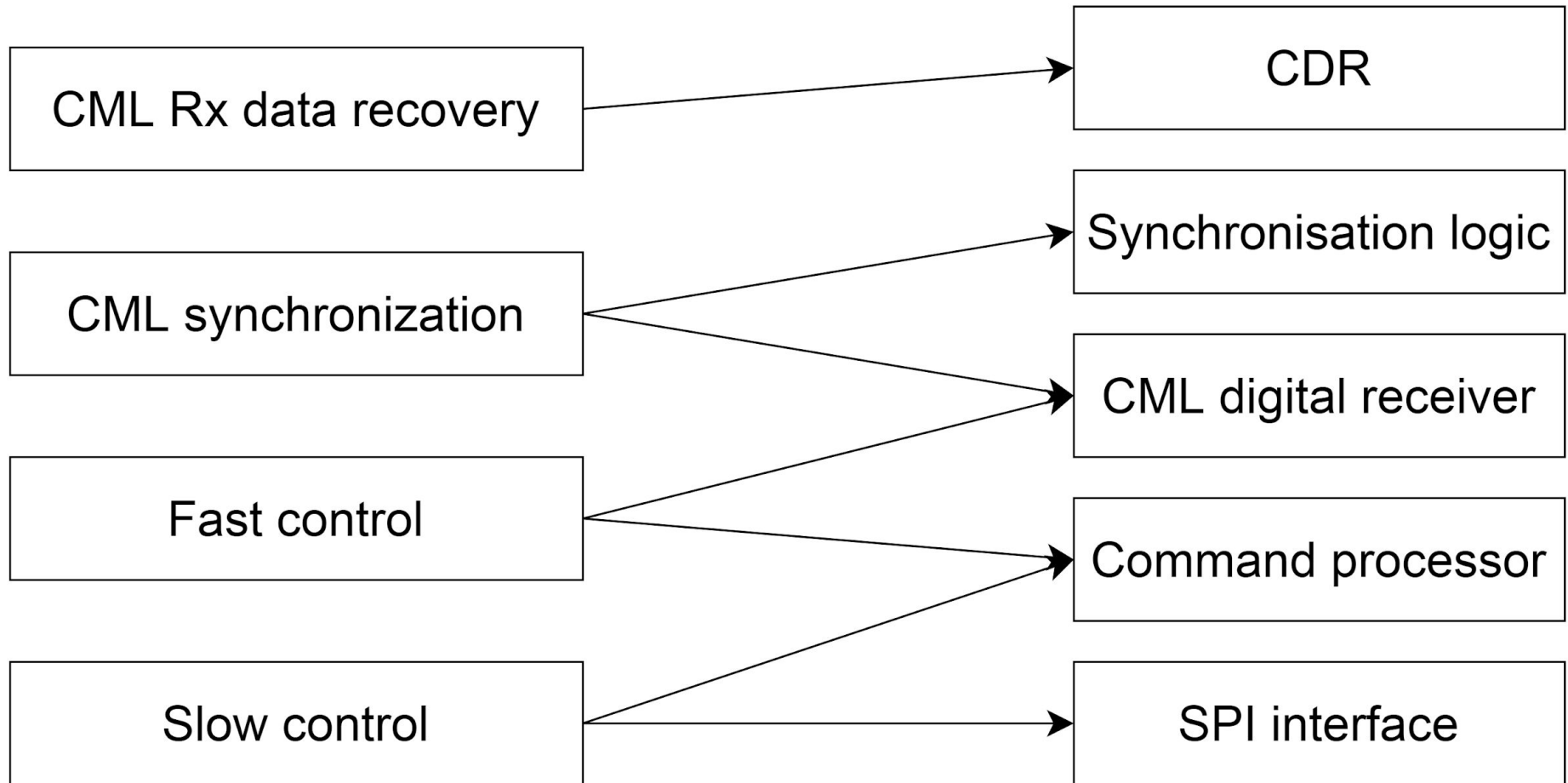
# blocks (1)



# Features

&

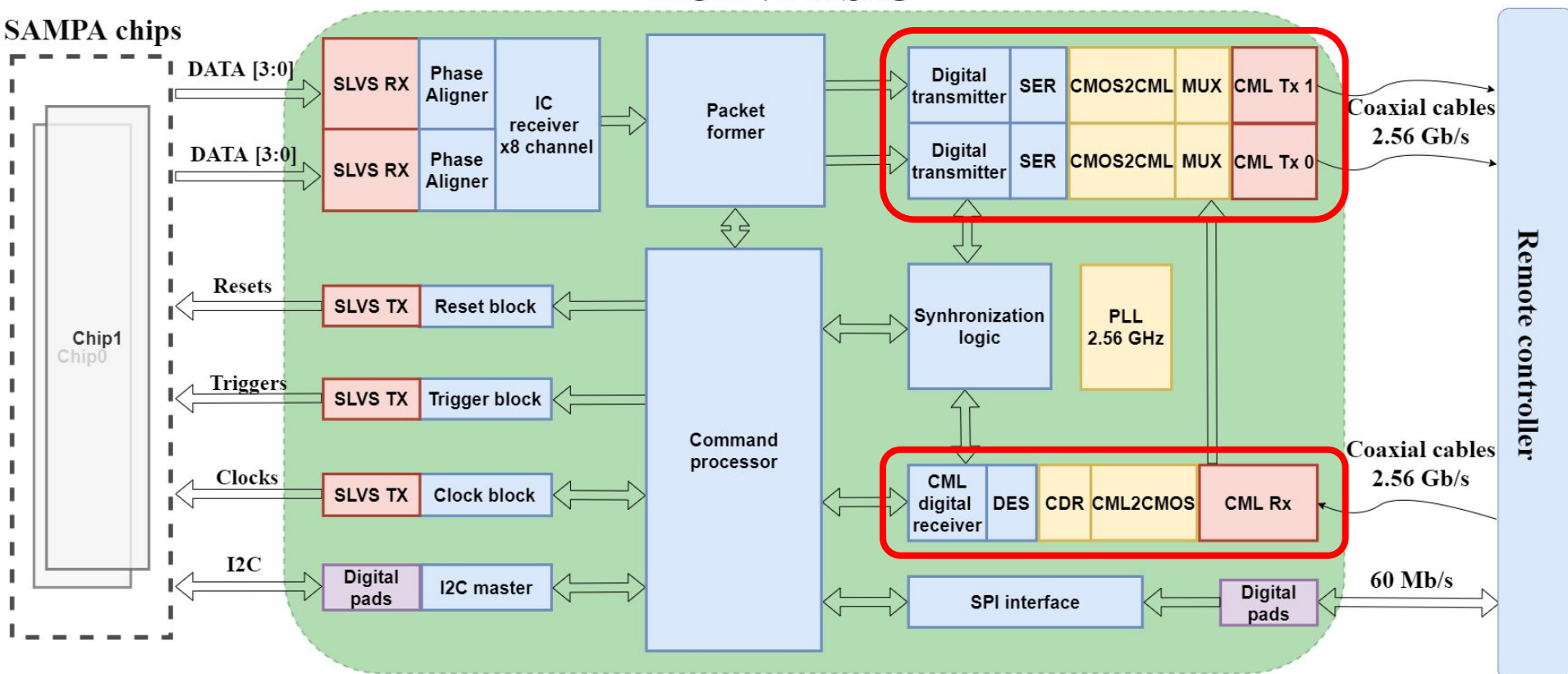
# blocks (2)





# High speed interface to counting room (1)

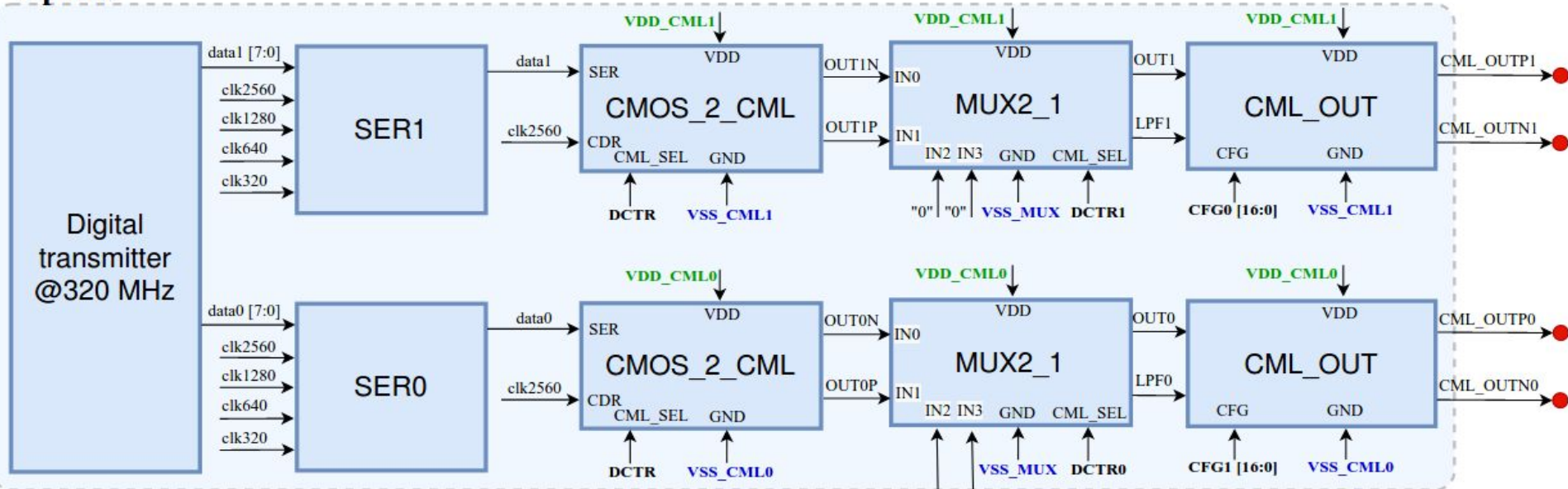
SAMPA chips



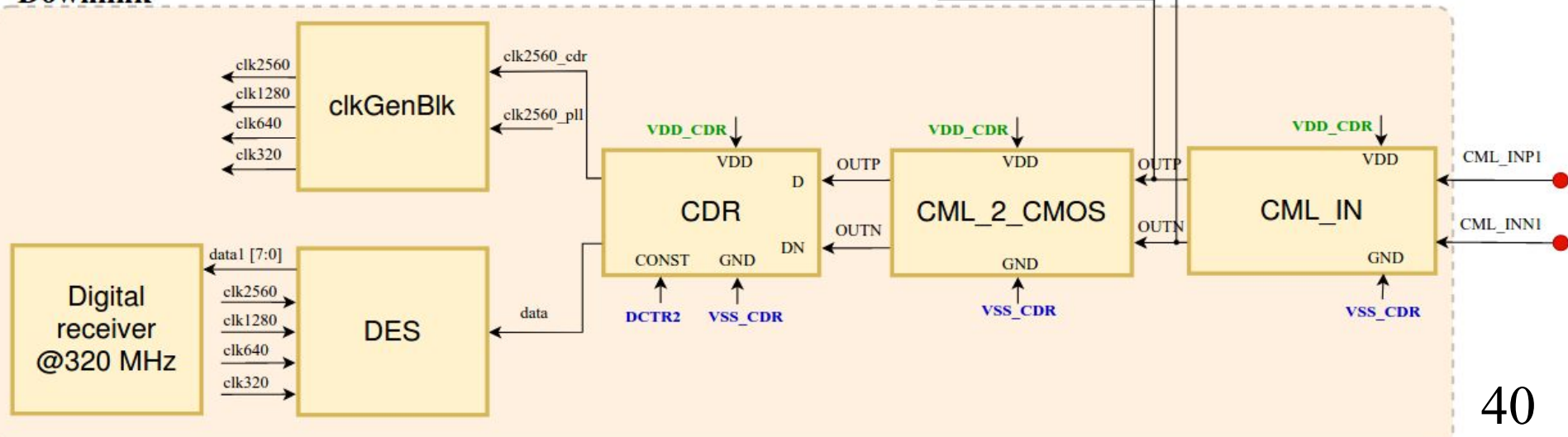
Mixed-mode (mostly digital (~70%)) design

# High speed interface to counting room (2)

## Uplink

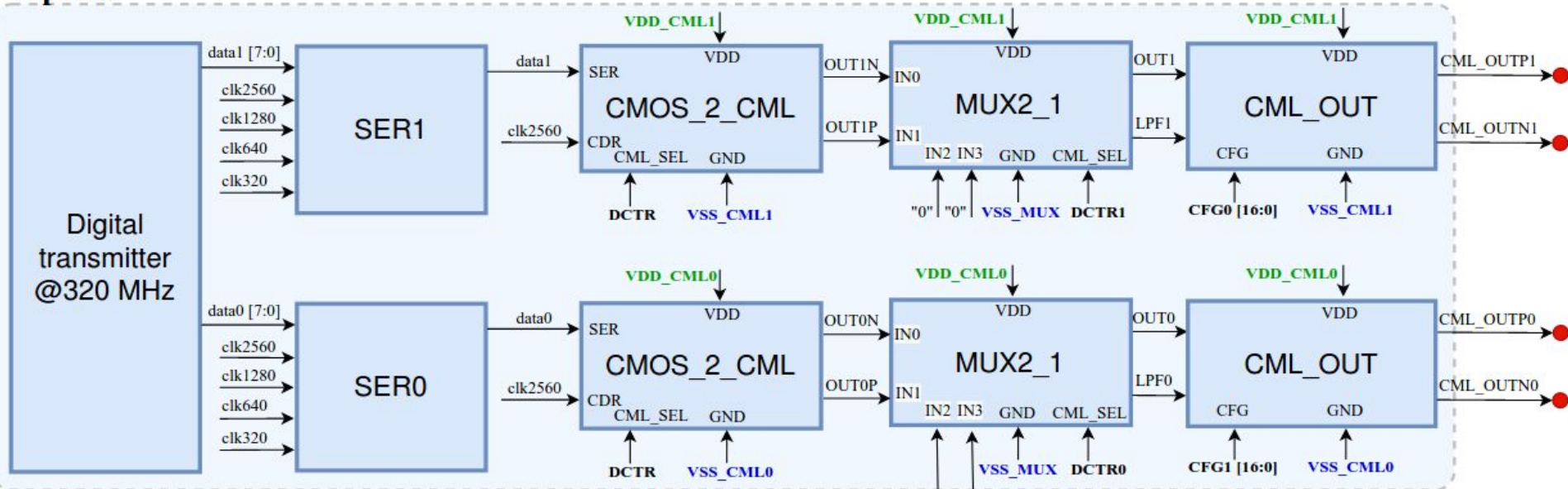


## Downlink

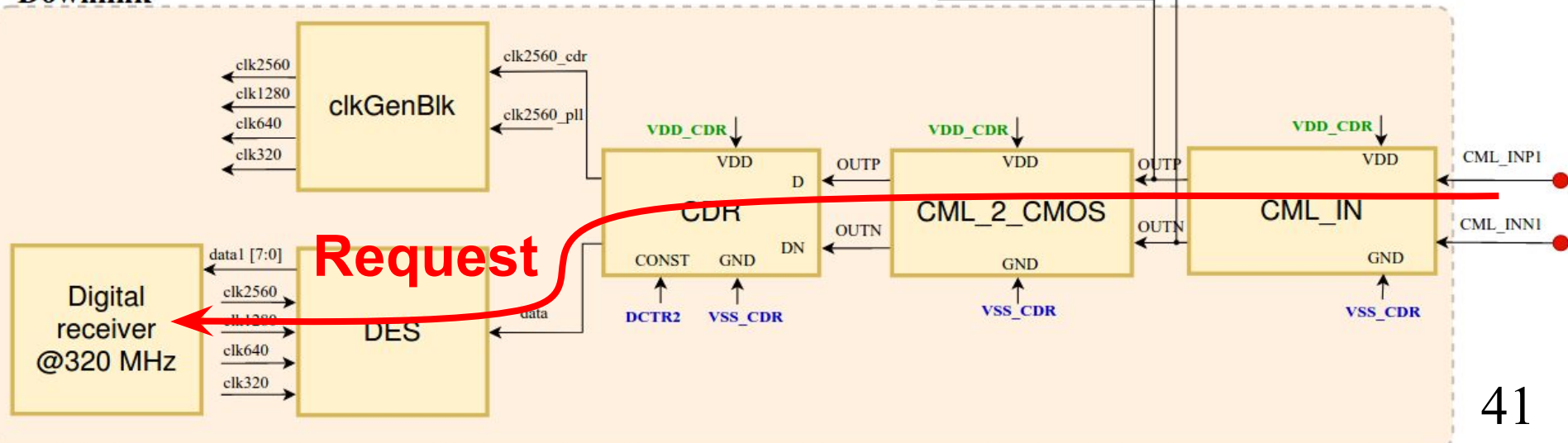


# High speed interface to counting room (2)

## Uplink



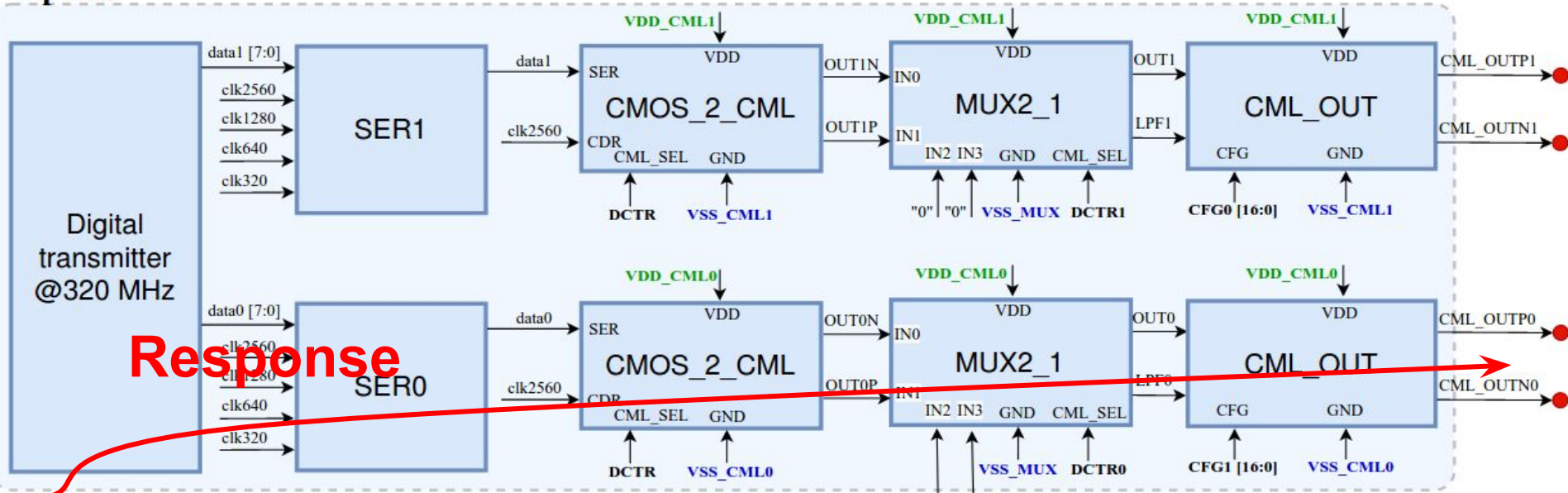
## Downlink



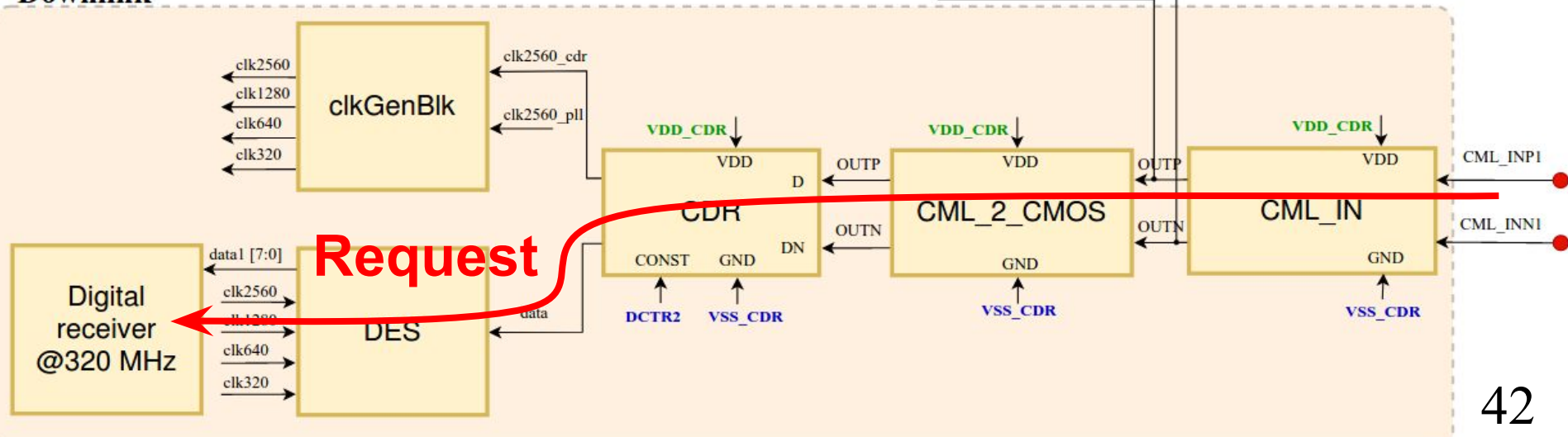


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## Uplink

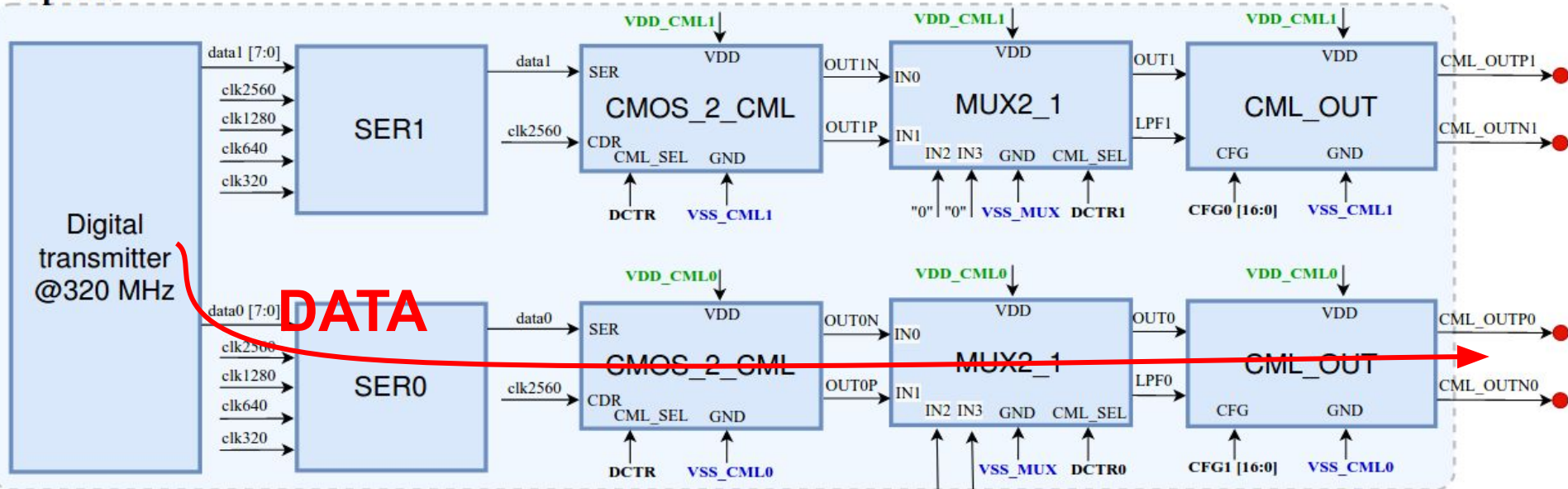


## Downlink

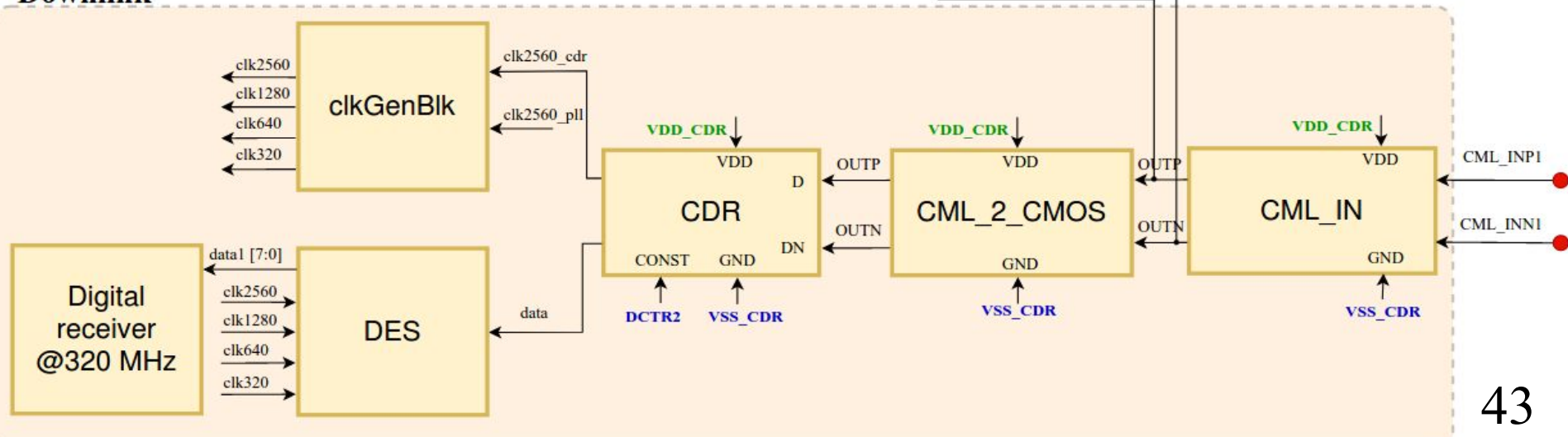


# High speed interface to counting room (2)

## Uplink

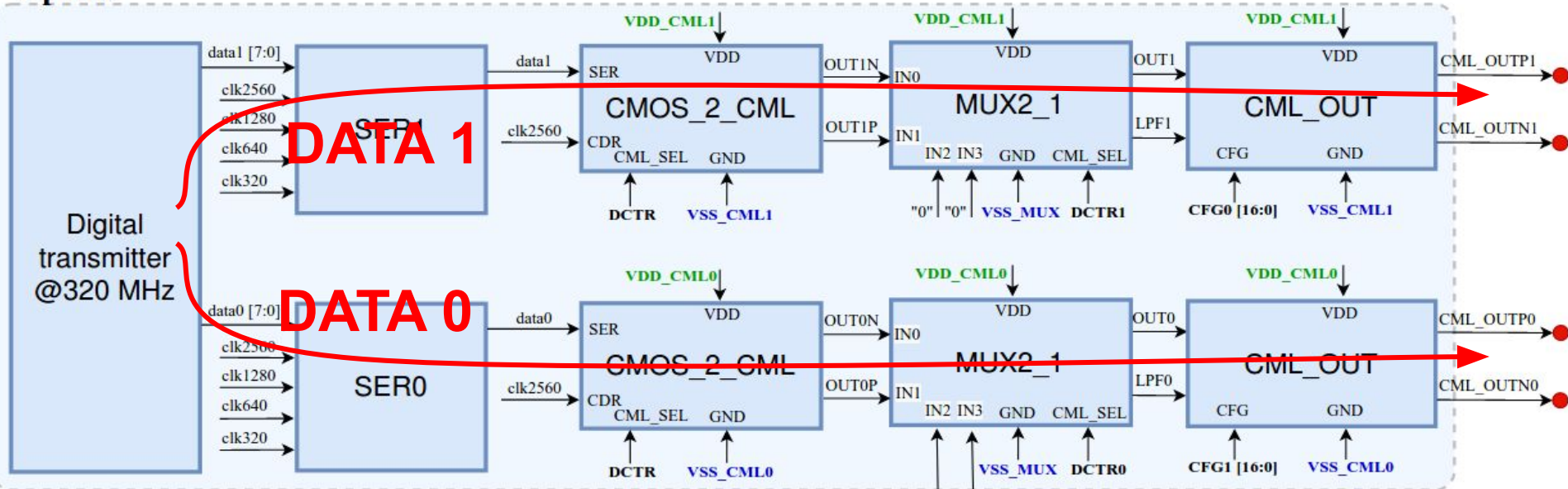


## Downlink

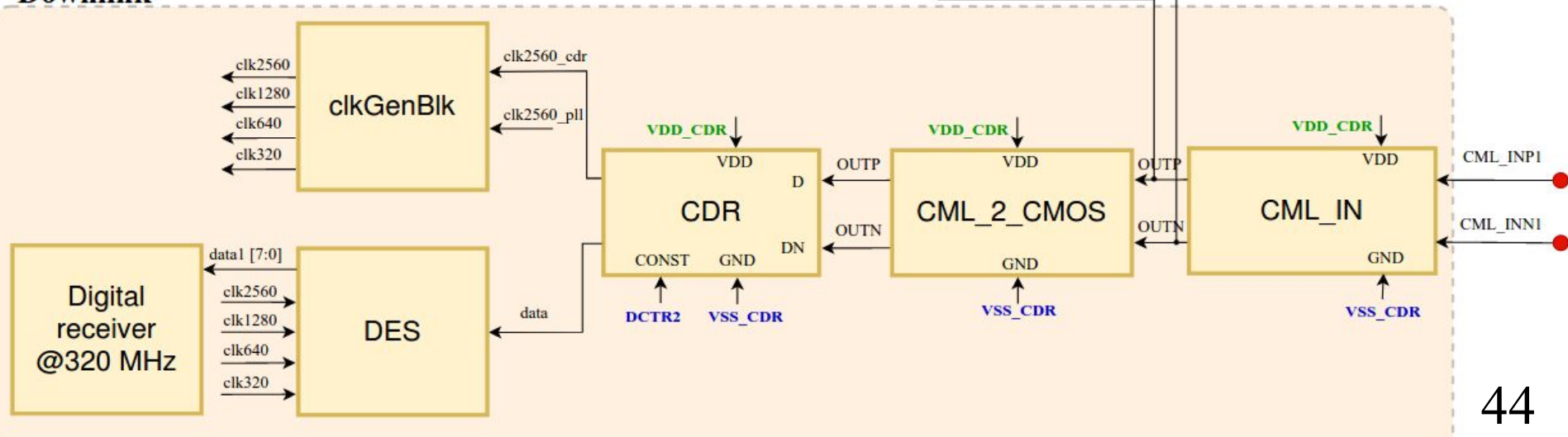


# High speed interface to counting room (2)

## Uplink



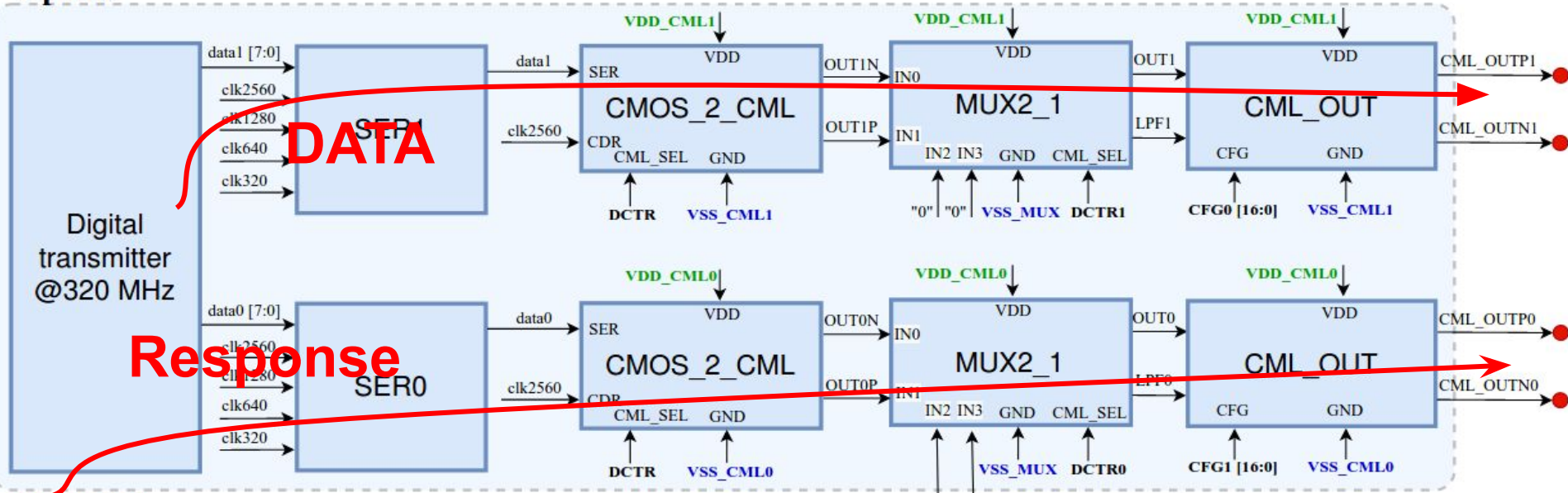
## Downlink



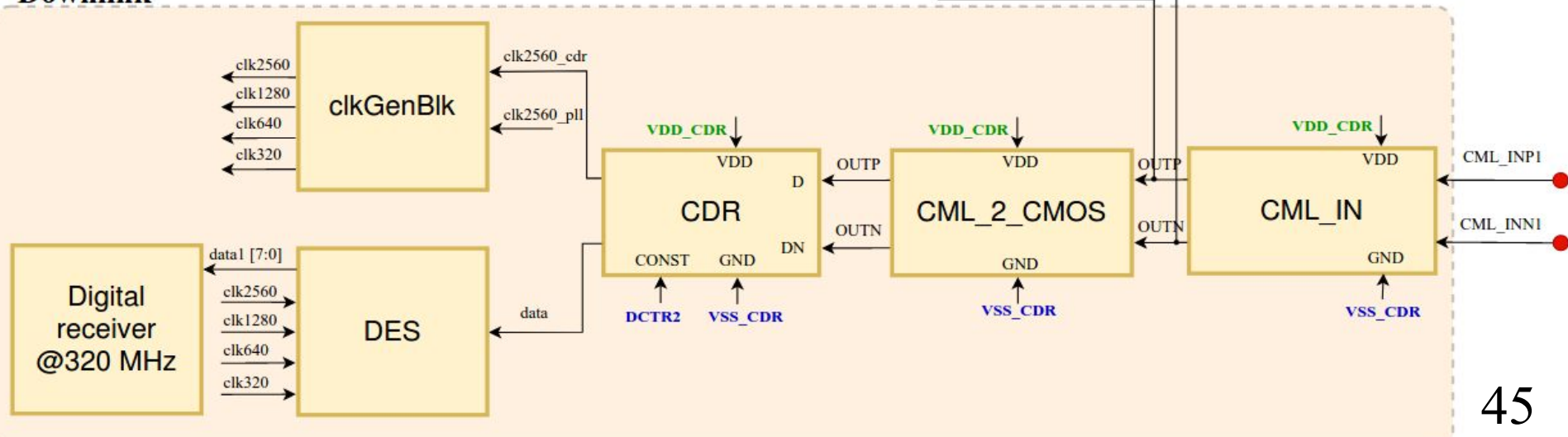


# High speed interface to counting room (2)

## Uplink



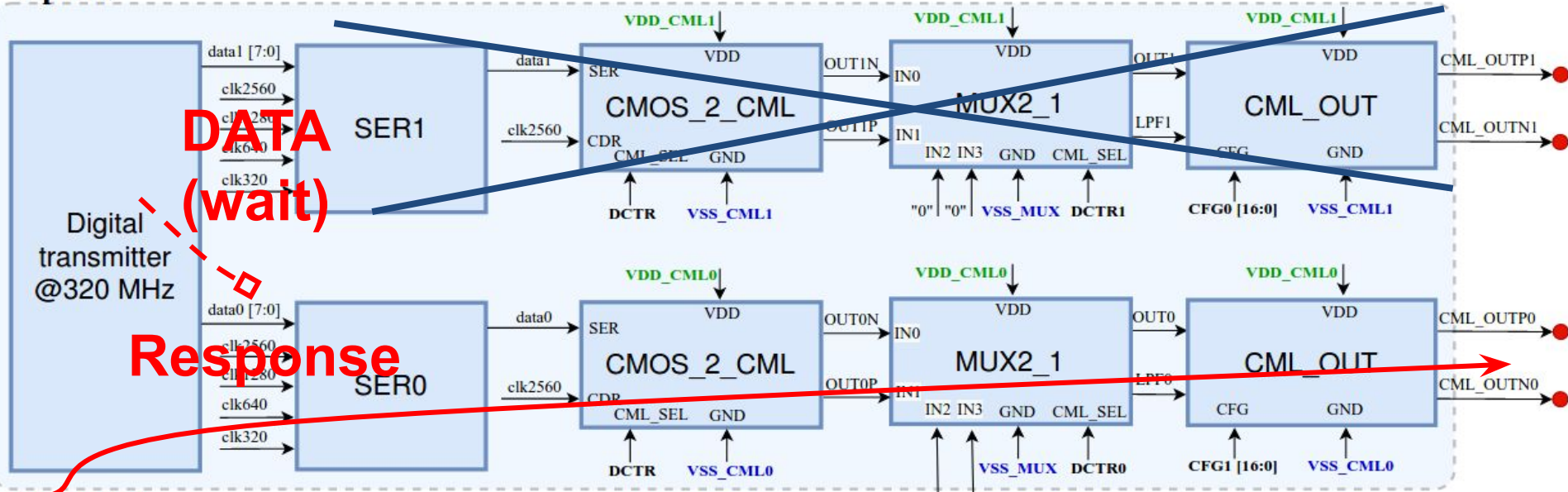
## Downlink



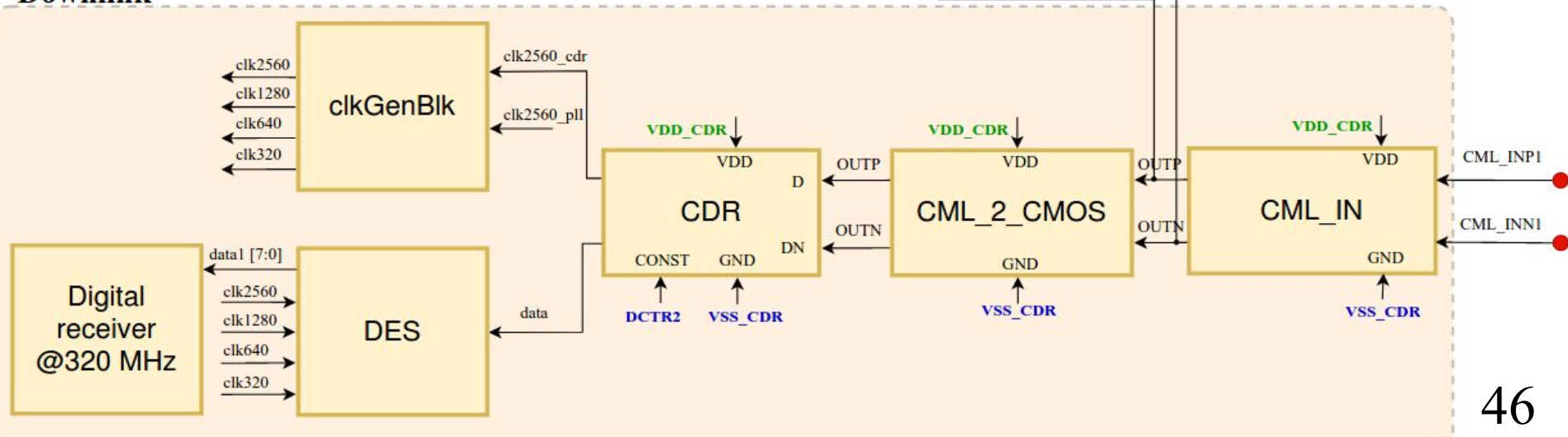
# High speed interface to counting room (3)

## (one CML mode)

### Uplink



### Downlink



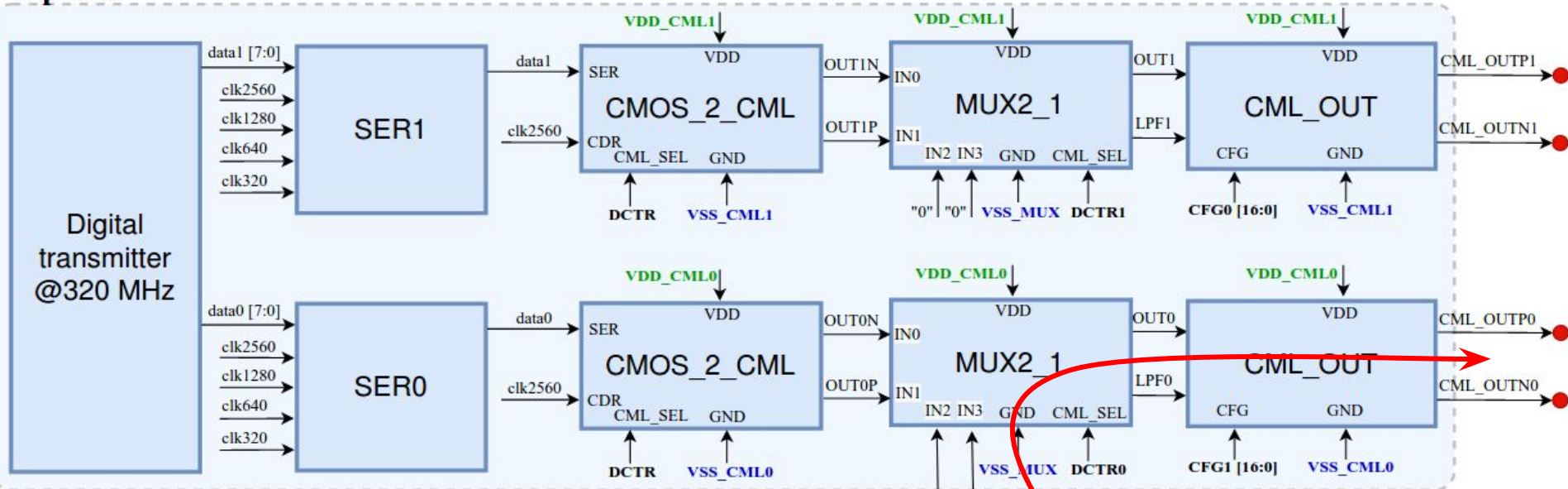
# High speed interface to counting room (4)

(main CML interface features)

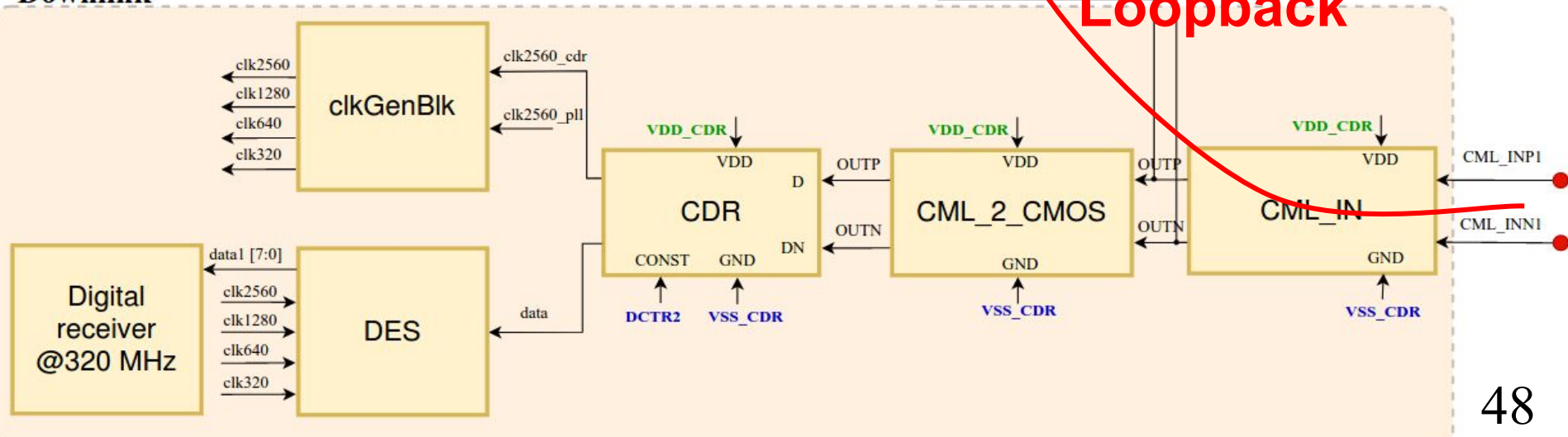
- CML data are encoded by 8b/10b
- CML Rx receives command request
- CML Tx 0 translates command response and SAMPA data  
(commands have higher priority than data)
- CML Tx 1 translates SAMPA data if CML Tx 0 is busy and two CML Tx are used

# High speed interface to counting room (loopback mode) (4)

## Uplink

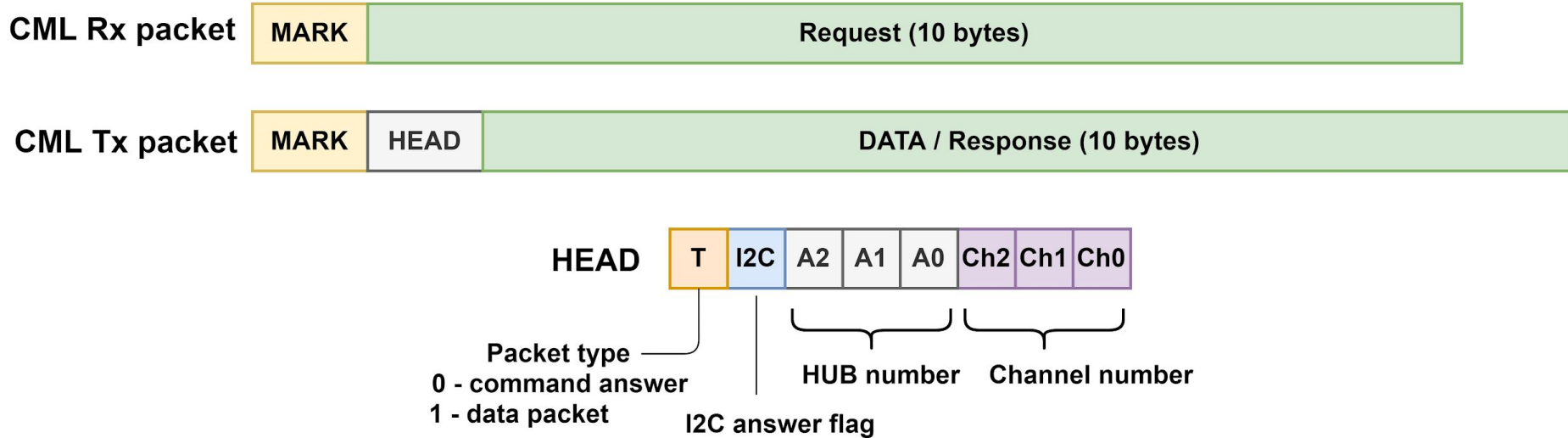


## Downlink





# CML protocol (1)

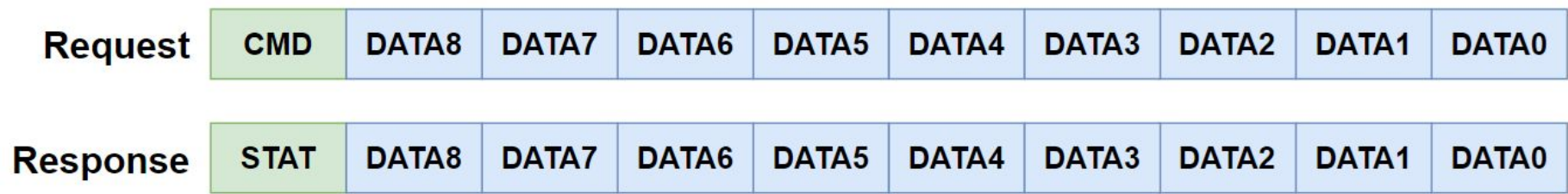


When T=0 then packet contains command Response

When T=1 then packet contains 10 bytes DATA

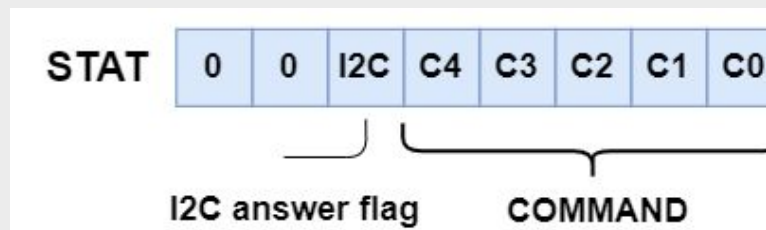
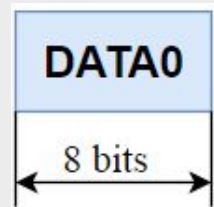
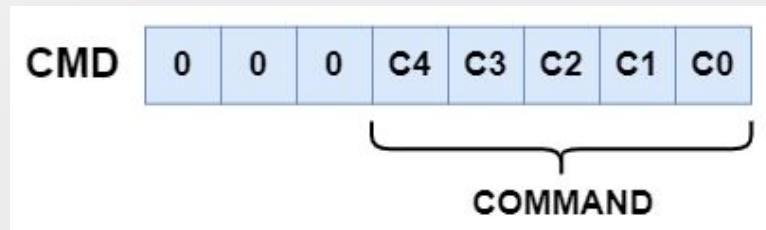
# CML protocol (2)

## Format of commands



### ***Commands:***

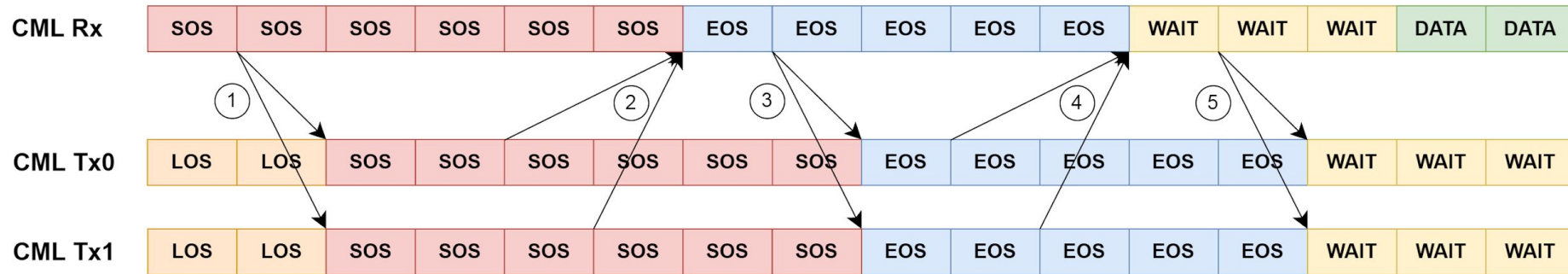
- Config load
- Config read
- ASIC Soft Reset
- SAMPA Trigger out
- SAMPA reset
- I2C read
- I2C write
- Debug commands





# CML protocol (3)

## Synchronization procedure



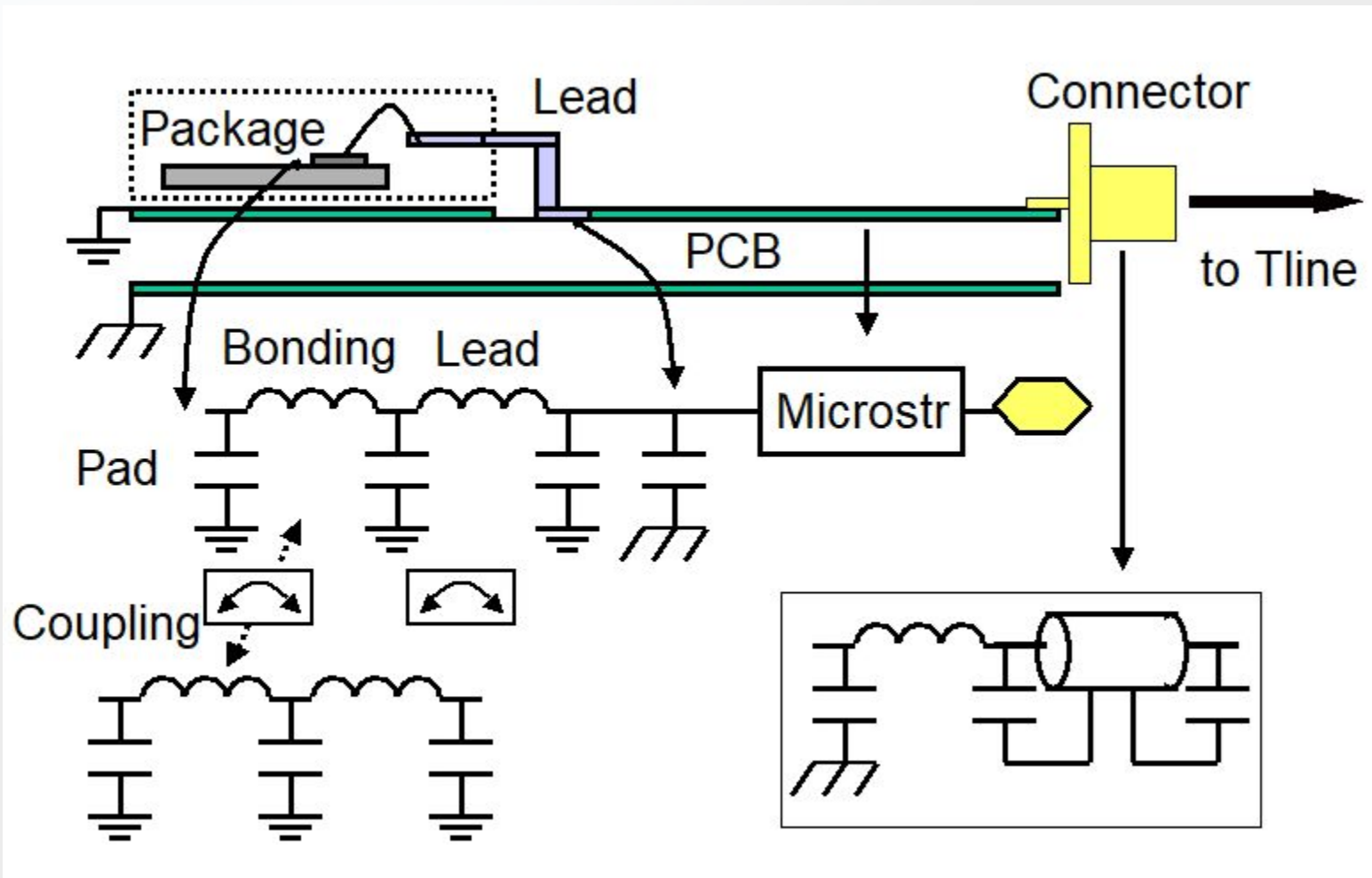
### Steps:

- 1) ASIC starts of synchronization
- 2) Controller synchronize both channels
- 3) ASIC sends EOS
- 4) Controller finalize synchronization
- 5) ASIC finalize synchronization

### CML modes:

- LOS (lost of sync) - K28.4
- SOS (start of sync) - K28.1
- EOS (end of sync) - K28.3
- WAIT - K28.5
- Data packet
- Command packet

# CML interface parasitics



# Some tips and tricks on radiation tolerance

Krohn M., Bentele B., Christian D., Cumalat J., Deptuch G., Fahim F., Hoff J., Shenai A., Wagner S. Radiation tolerance of 65nm CMOS transistors // J. of Instr., 2015, V.10, pp. C05009.

Bucher M., Nikolaou A., Papadopoulou A., Makris N., Chevas L., Borghello G., Koch H., Faccio F. Total Ionizing Dose Effects on Analog Performance of 65 nm Bulk CMOS with Enclosed-Gate and Standard Layout // 2018, at International Conference on microelectronic test structures, Austin, USA.

Bonacini, P. Valerio, R., Avramidou R., Ballabriga R., Faccio F., Kloukinas K., Marchioro A. Characterization of a commercial 65 nm CMOS technology for SLHC applications // JINST, 2012, V.7, pp. P01015.

Kulis S., Jara Casas L., Ceresa D., Miryala S., Christianses J., Francisco R., Gnani D. Characterization of radiation effects in 65 nm digital circuits with the DRAD digital radiation test chip // J. of Instr., 2017, V.12, pp. C02039-C02039.

Lacoe R., Improving Integrated Circuit Performance Through the Application of Hardness-by-Design Methodology // IEEE Transactions on Nuclear Science, 2008, V.55, pp. 1903-1925.

Fleetwood D., Total Ionizing Dose Effects in MOS and Low-Dose-Rate-Sensitive Linear-Bipolar Devices // IEEE Transactions on Nuclear Science, 2013, V.60, pp. 1706-1730.

Claeys C., Simoen E., Physics and Modeling of Radiation Effects in Advanced CMOS Technology Nodes. // Simulation of Semiconductor Processes and Devices, Springer, 2004, pp.181-190.

Camplani A. Shojaii S., Shrimali H., Stabile A., Liberali V. CMOS IC Radiation Hardening by Design, 2014, V.27, pp. 251-258.

Seixas L., Goncalvez O., Souza R., Finco S., Vaz R., da Silva G., Gimenez S. Improving MOSFETs' TID Tolerance Through Diamond Layout Style // IEEE Transactions on Device and Materials Reliability, 2017, V.17, pp. 593-595.

Faccio F. Michelis S., Cornale D., Paccagnella A., Gerardin S. Radiation-induced short channel (RISCE) and narrow channel (RINCE) effects in 65 and 130 nm MOSFETs // IEEE Trans. Nucl. Sci., 2015, V.62, pp. 2933-2940.

Menouni M., Barbero M., Bompard F., Bonacini S., Fougeron D., Gaglione R., Pozanov A., Valerio P., Wang A. 1-Grad total dose evaluation of 65nm CMOS technology for the HL-LHC upgrades // J. of Instr., 2015, V.10, pp. C05009.

Lee M., Lee H. "Dummy Gate-Assisted n-MOSFET Layout for a Radiation-Tolerant Integrated Circuit // IEEE Transactions on Nuclear Science, 2013, V.60, pp. 3084-3091.

Díez-Acereda V., Khemchandani S., del Pino J., Mateos-Angulo S. RHBD Techniques to Mitigate SEU and SET in CMOS Frequency Synthesizers // Electronics, 2019, V.8 p. 690.

Maurice G. et al. (RD53 Collab.) The RD53A Integrated Circuit // CERN-RD53-PUB-17-001, 2019, Version 3.51.